

Description

The present invention relates to the bonding of a metal wire to a bonding site, such as an external terminal and/or a lead of a semiconductor chip. It is primarily concerned with the bonding of wires coated with an insulator.

The present invention is applied to a method of bonding, and an apparatus for bonding.

Wire is used for the connection between a semiconductor chip and lead of a resin-encapsulated semiconductor device. The wire is joined to the chip and lead by a wire-bonding apparatus.

The wire is wound round a spool of the bonding apparatus, and is supplied from the spool to a bonding site through a tensioner, a wire clasper, a bonding tool, etc. The bonding apparatus is constructed so that the wire (which normally has a ball at the free end thereof) is joined to the external terminal (bonding pad) of the semiconductor chip (pellet). A further part, such as the other end of the wire of predetermined length, may then be joined to the lead which is an external drawing-out lead formed in a lead frame. Bonding of the free end is achieved by a "ball bonding" technique. The ball at the end of the wire may be formed by thermal energy generated when an electric torch (an arc electrode) is brought near to the end of the wire so as to establish electric arcs between the torch and the wire. US-A-4 564 734 discloses a method of "ball-bonding" uncoated wires, and forms the basis of the pre-characterising parts of the claims.

It is common to use a coated wire. The coated wire may be a metal wire of gold (Au), copper (Cu), aluminium (Al) or the like coated with an electric insulator made of a resin material such as polyurethane resin, ester imide resin, or polyimide resin. Oxide films, such as CuO, Cu₂O, or Al₂O₃ may also be used. This insulator prevents contact between individual wires, or contact between the wire and the semiconductor chip, etc. when the semiconductor device has been encapsulated with a resin for the purpose of packaging.

When joining the coated wire to the bonding site, e.g. an external terminal of the semiconductor chip or a lead, the insulator of the coating at the part of the coated wire to be joined needs to be removed. The removal of the insulator is naturally intended to ensure the electrical connection and perfect continuity between the coated wire and the external terminal or lead.

One technique for removing the insulator of the coated wire is disclosed in the official gazette of Japanese Patent Application Laid-open No. 194735/1986 the application of which has been filed by the same applicant before. This technique consists in that the insulator of the bonding part of the coated wire is irradiated with a laser beam so as to be decomposed (melted) and removed.

As the result of the study of the above technique, however, the inventors have found out that when the coated wire is unidirectionally irradiated with the laser beam to remove the insulator, in insulator of the bonding part of the coated wire directly irradiated with the laser beam is removed reliably. It is impossible, however, to remove the insulator from the coated wire on the opposite side of the wire to the beam, on which the laser beam is not incident. Therefore, some insulator remains and a bonding defect arises.

The present invention seeks to overcome this problem and so increase the reliability of bonding. It proposes that heat is applied to the wire, which causes the insulator to melt. This causes vapor to be given off, which vapor is evacuated from the bonding suite by a suction nozzle. This prevents the insulating film condensing on the bond and adversely affecting the reliability of the bond. The present invention may thus provide a method of bonding a metal wire to a semiconductor device; the device having a semiconductor chip with at least one bonding site on a major surface thereof and at least one lead; the method using a bonder having a bonding stage, a capillary, a spool coiled with a wire coated by an insulating film of an organic resin and a discharge electrode; the method comprising the steps of:

- (a) placing the chip on the bonding stage;
- (b) causing one end of the wire to project through the capillary;
- (c) generating an arc discharge between the one end of the wire projecting through the capillary and the electrode by applying a first electric potential to the other end of the wire coiled on the spool and a second electric potential to the electrode to form a ball on the one end of the wire; and then
- (d) bonding the wire to the bonding site by pressing the ball against the bonding site using the capillary;

wherein:

the step (c) is performed while vapor of the organic resin, which vapor is produced by the heat of the arc discharge, is evacuated through a first evacuating nozzle adjacent to the one end of the wire to prevent the vapor from condensing on or in the capillary.

Another embodiment of the invention may provide a method of bonding a metal wire to a semiconductor device; the device having a semiconductor chip with at least one bonding site on a major surface thereof and at least one lead; the method using a bonder having a bonding stage, a capillary, a spool coiled with a wire coated by an insulating film of an organic resin and a discharge electrode; the method comprising the steps of:

- (a) placing the chip on the bonding stage;
- (b) causing one end of the wire to project through the capillary;
- (c) generating an arc discharge between the one end of the wire projecting through the capillary and the electrode by applying a first electric potential to the other end of the wire coiled on the spool and a second electric potential to the electrode to form a ball on the one end of the wire; and then
- (d) bonding the wire to the bonding site by pressing the ball against the bonding site using the capillary; wherein:

steps (c) and (d) are performed while the other end of the wire is connected to a common ground of the bonder to prevent a discharge between the wire and the bonder or through the chip.

- (e) removing the insulating film of the wire by vaporising the insulating film with heat over a predetermined length at a predetermined point of the wire between the one and the other ends of the wire to be bonded to the lead while the one end of the wire protrudes out of the capillary; and then
- (f) wedge-bonding the predetermined point of the wire to the lead by pressing the predetermined point of the wire against the lead with the capillary;

wherein:

the step (e) is performed while vapor of the organic resin, which vapor is produced by the heat, is evacuated through a second evacuating nozzle adjacent to the predetermined point of the wire to prevent the vapor from condensing on or in the bonder.

The present invention may thus provide an apparatus for bonding a metal wire coated by an organic insulating film to an electronic device, the device having a semiconductor chip with at least one bonding site on a major surface thereof and at least one lead; said apparatus comprising:

- (a) a wire bonding stage for receiving the chip;
- (b) a bonding wire coated by an organic insulating film coiled on a spool, and a bonding capillary arranged so as to permit one end of the wire to project from a lower tip thereof through its bore;
- (c) a discharge electrode above the stage;
- (d) an arc voltage generator for generating an arc discharge through a gap between the one end of the wire projecting through the capillary and the electrode by applying a first electric potential to the wire via the other end of the wire coiled on the spool, and a second electric potential to the electrode thereby to form a ball at the one end of the wire; and
- (e) a control means for bonding the wire to the bonding site on the chip by pressing the ball against the site with the lower tip of the capillary;

wherein the apparatus further comprises an evacuating nozzle adjacent to the lower tip of the capillary for evacuating vapor of the organic film produced by the heat of the arc discharge.

Alternatively the present invention may provide an apparatus for bonding a metal wire coated by an organic insulating film to an electronic device, the device having a semiconductor chip with at least one bonding site on a major surface thereof and at least one lead; said apparatus comprising:

- (a) a wire bonding stage for receiving the chip;
- (b) a bonding wire coated by an organic insulating film coiled on a spool, and a bonding capillary arranged so as to permit one end of the wire to project from a lower tip thereof through its bore;
- (c) a discharge electrode above the stage;
- (d) an arc voltage generator for generating an arc discharge through a gap between the one end of the wire projecting through the capillary and the electrode by applying a first electric potential to the wire via the other end of the wire coiled on the spool and a second electric potential to the electrode thereby to form a ball at the one end of the wire; and
- (e) a control means for bonding the wire to the bonding site on the chip by pressing the ball against the site with the lower tip of the capillary;

wherein the apparatus further comprises:

- (f) a torch for generating heat to remove the insulating film over a predetermined length at a predetermined point of the wire between the one and the other ends of the wire to be wedge-bonded by the capillary, while the one end of the wire protrudes out of the lower tip of the capillary;
- (g) an evacuating nozzle for evacuating vapor of the insulating film produced by the heat during the removal of the insulating film at the predetermined point of the wire to prevent the vapor from condensing on or in the bonder; and
- (h) a control means for wedge-bonding the predetermined point of the wire to the lead by pressing the predetermined point of the wire against the lead with the capillary.

Embodiments of the invention will now be described in detail, by way of example, with reference to the accompanying drawings, in which:

Fig. 1 is a schematic constructional view of a ball-bonding apparatus which is Embodiment 1 of the present

invention;

Fig. 2 is a perspective view of the essential portions of the bonding apparatus

Fig. 3 is a sectional view of a resin-encapsulated semiconductor device which has been bonded by the bonding apparatus;

Fig. 4 is a sectional view of the essential portions of the resin-encapsulated semiconductor device;

Fig. 5 is an enlarged perspective view of the essential portions of the bonding apparatus;

Fig. 6 is an exploded perspective view of the essential portions of the bonding apparatus;

Fig. 7 is an enlarged perspective view of the essential portions of the bonding apparatus;

Fig. 8 is a sectional view of the essential portions of the bonding apparatus;

Fig. 9 is a perspective view of the essential portions of the bonding apparatus;

Figs. 10 and 11 are graphs each showing the relationship between the melting point of the metal wire and the decomposition temperature of a coated wire which is used in the bonding apparatus; and

Fig. 12 is a graph showing the relationship between the applied voltage of the heating wire of a heater and the temperature of burning flames blown off from an outlet in the insulator removal torch of the bonding apparatus.

Further, Fig. 13 is a schematic constructional view of a ball-bonding apparatus which is Embodiment 5 of the present invention;

Fig. 14 is a perspective view of the essential portions of the ball-bonding apparatus;

Fig. 15 is a sectional view of a resin-encapsulated semiconductor device;

Fig. 16 is an enlarged sectional view of the essential portions of the resin-encapsulated semiconductor device;

Fig. 17 is a partial sectional view showing the practicable construction of the essential portions of the ball-bonding apparatus;

Fig. 18 is a plan view taken in the direction of arrow XVII in Fig. 17;

Fig. 19 is a sectional view taken along cutting-plane line XIX-XIX in Fig. 18;

Fig. 20 is a model-like constructional view for explaining the principle of the formation of a metal ball;

Fig. 21 is an exploded perspective view of the essential portions of the spool of the ball-bonding apparatus;

Fig. 22 is an enlarged perspective view of the essential portions of the spool;

Fig. 23 is a graph showing the relationship between the magnitude of energy of electric arcs and the magnitude of shrinkable melting of the insulator of a coated wire;

Fig. 24 is a graph showing the relationship between the temperature of a fluid and the magnitude of shrinkable melting of the insulator of the coated wire;

Fig. 25 is a partial sectional view showing the essential portions of a ball-bonding apparatus which is Embodiment 6 of the present invention; and

Fig. 26 is a plan view taken in the direction of arrow XIV in Fig. 25.

Several embodiments to be disclosed in this section will be briefly summarized to assist understanding of the present invention.

The outlines of Embodiments 1 thru 4 are as follows:

In bonding technology which uses a coated wire, a mixed gas consisting of a combustible gas and a temperature controlling gas for lowering the combustion temperature of the combustible gas is prepared, and using combustion flames obtained by burning the combustible gas of the mixed gas, an insulator in the bonding part of the coated wire is removed to denude the surface of a metal wire. The removal of the insulator is performed with an insulator removal torch.

In addition, the metal wire of the coated wire from which the insulator has been removed is formed into a metal ball by the use of the combustion flames stated above or combustion flames formed by burning another mixed gas.

Besides, a heater is provided near the blowoff outlet of the insulator removal torch for the combustible gas.

Besides, the dimensions of the blowoff outlet of the insulator removal torch for the combustible gas are made small.

Further, in bonding technology wherein electric arcs are struck across an arc electrode and the metal wire of a coated wire at the front end thereof, so as to form a metal ball at the front end of the coated wire, the metal wire of the coated wire is connected to a positive electrode, and the arc electrode is connected to a negative electrode.

According to the above-stated expedients, the combustion flames which do not impose any damage or breakdown on the metal wire can be turned round substantially the whole area of the bonding part of the coated wire, so that the insulator of the coated wire can be reliably removed to lessen bonding defects.

In addition, since the metal ball of the coated wire is formed by the combustion flames, an arc electrode and an arcing unit can be dispensed with.

Besides, the combustion flames of the combustible gas can be reliably formed at the blowoff outlet of the insulator removal torch for the combustible gas, so that the insulator of the coated wire can be reliably removed to lessen bonding defects.

Besides, the heat capacity of the combustion flames burning at the blowoff outlet of the insulator removal torch for the combustible gas can be made small, so that the insulator of the coated wire which is supplied near the flames can be prevented from damaging or breaking down.

Further, the appearing position of the electric arcs which are struck across the arc electrode and the metal wire of the coated wire is stabilized, and the damage or breakdown of the insulator of the coated wire attributed to the upward crawl of the electric arcs can be prevented, so that the withstand voltage of the coated wire can be raised to enhance the reliability of the bonding technology.

On the other hand, the outlines of Embodiments 5 and 6 are as follows:

In a semiconductor device which uses a coated wire, a metal ball formed at one end side of the coated wire is joined to the external terminal of a semiconductor chip, and a metal wire on the other end side of the coated wire in a contact part where an insulator has been destroyed is joined to a lead.

In addition, in bonding technology which uses a coated wire, a metal ball is formed on the front end side of the coated wire, the metal ball is joined to the external terminal of a semiconductor chip, the rear end side of the coated wire is brought into contact with a lead, an insulator in the contact part is destroyed, and a metal wire on the other end side of the coated wire is joined to the lead.

In bonding technology wherein a metal ball is formed at the front end of a coated wire, a fluid blast equipment for blasting a fluid against the front end part of the coated wire is disposed near the front end of the coated wire.

In the bonding technology wherein a metal ball is formed at the front end of a coated wire, the fluid blast equipment stated above is disposed, and a suction equipment for imbibing that insulator of the coated wire which is blown away by the blast of the fluid from the fluid blast equipment is disposed near the front end of the coated wire.

In the bonding technology wherein a metal ball is formed at the front end of a coated wire, the fluid blast equipment stated above is disposed, and a cooler for cooling the fluid of the fluid blast equipment is disposed.

According to the above-stated expedients, the area of contact between the external terminal of the semiconductor chip and the metal wire of the coated wire increases, so that the bondability between the two can be enhanced, and the coated wire except the part to be joined with the lead is held coated with the insulator so as to mitigate the short-circuit of this coated wire with another coated wire adjacent thereto, so that the intervals of the leads can be shortened to enlarge the number of the terminals of the semiconductor device.

In addition, an insulator removal torch which removes the insulator of the coated wire on the rear end side thereof, and a moving mechanism, a controller etc. for the torch can be curtailed, so that the structure of a bonding apparatus can be simplified.

Besides, the melting and shrinking insulator of the coated wire is blown away, and insulator globes can be prevented from being formed in the coated wire, so that a bonding defect is avoidable.

Besides, since the melting and shrinking insulator of the coated wire can be blown away to prevent insulator globes from being formed in the coated wire, a bonding defect is avoidable, and since the insulator blown away is not scattered to the bonding part, a bonding defect ascribable to the scattered insulator is avoidable.

Besides, the shrinkable melting of the insulator of the coated wire is remarkably reduced, and even when the insulator has melted and shrunk, it can be blown away, so that insulator globes can be prevented from being formed in the coated wire, and a bonding defect can be avoided.

Embodiment 1:

A ball-bonding apparatus which is Embodiment 1 of the present invention is illustrated in Fig. 1 (a schematic constructional view) and Fig. 2 (a perspective view of essential portions).

As shown in Fig. 1, the bonding apparatus is so constructed that a coated wire 2 wound round a spool 1 is supplied to a bonding space 3. The supply of the coated wire 2 to the bonding space 3 is performed through a tensioner 4, a wire guide member 5, a wire clasper 6 and a bonding tool (capillary) 7.

In the bonding space 3, a resin-encapsulated type semiconductor device 12 before resin encapsulation to be constructed as shown in Fig. 3 (a sectional view) and Fig. 4 (a sectional view of essential portions) is arranged. The resin-encapsulated semiconductor device 12 is so constructed that a semiconductor chip 12A placed on a tab portion 12C through a connecting metal film 12B and the inner lead parts of leads 12D are encapsulated by a resin mold member 12E. The semiconductor chip 12A and the lead 12D are connected by the coated wire 2. One end of the coated wire 2 is joined to an external terminal (bonding pad) 12Aa which is exposed through an opening provided in the passivation film 12Ab of the semiconductor chip 12A. The other

end of the coated wire 2 is joined to the inner lead part of the lead 12D as stated before. The outer lead part of the lead 12D is formed so as to protrude outside the resin mold member 12E. The resin-encapsulated type semi-conductor device 12 before the resin encapsulation step is supported on a semiconductor device bed 13.

As shown in detail in Fig. 4, the coated wire 2 is so constructed that the surface of a metal wire 2A is coated with an insulator 2B. The metal wire 2A is made of gold (Au) in the present embodiment. Alternatively, the metal wire 2A is made of copper (Cu), aluminum (Al) or the like. The insulator 2B is formed of a polyurethane resin film or a polyimide resin film in the present embodiment. Alternatively, the insulator 2B is formed of a resin film such as ester imide resin film or ester amide resin film, or a metal oxide film (of CuO, Cu₂O or Al₂O₃).

The front end of the coated wire 2 on the supply side thereof, which lies in front of the bonding tool 7, is formed with a metal ball 2Aa. As shown in Fig. 1, Fig. 2 and Fig. 5 (an enlarged perspective view of essential portions), the metal ball 2Aa is formed by an arc electrode 10 which is disposed at a position close to the bonding tool 7. That is, the metal ball 2Aa is formed by striking electric arcs across the metal wire 2A at the supply-side front end of the coated wire 2 and the arc electrode 10. The arc electrode 10 is connected to an arcing circuit (or arcing unit) 11 shown in Fig. 2.

The arcing circuit 11 is principally constructed of a capacitor C₁, a storage capacitor C₂, an arcing thyristor D which is actuated by a trigger, and a resistor R. A d.c. power source DC is arranged so as to feed a voltage of negative polarity at, for example, approximately -1000 -- -3000 [V]. The d.c. power source DC is connected to the arc electrode 10 through the thyristor D, the resistor R, etc. A reference potential GND is, for example, the ground potential (= 0 [V]). Letter V indicates a voltmeter, and letter A an ammeter. As will be described in detail later, the metal wire 2A of the coated wire 2 is connected to the reference potential GND at its end part wound round the spool 1.

The arc electrode 10 is adapted to come near to the supply-side front end of the coated wire 2 when the metal 2Aa is to be formed, and to move away from the supply path of the coated wire 2 (in the direction of arrow A indicated in Fig. 2) during the bonding step. The movement of the arc electrode 10 is carried out by a first moving mechanism which is constructed of a crank 10A for turning the arc electrode 10 in the direction of the arrow A, a shaft 10B for rotating the crank 10A, and an electric solenoid 10C for shifting the shaft 10B in the direction of arrow B. The crank 10A is rotatably supported by a bonding apparatus proper 9.

In the bonding apparatus wherein, in this manner, the electric arcs are struck across the metal wire 2A at the front end of the coated wire 2 and the arc electrode 10 so as to form the metal ball 2Aa at the front end of the coated wire 2, the metal wire 2A of the coated wire 2 is connected to a positive electrode (+), and the arc electrode 10 is connected to a negative electrode (-), whereby the appearing position of the electric arcs struck across the metal wire 2A of the coated wire 2 and the arc electrode 10 can be stabilized more than in case of the opposite polarity, and hence, the upward crawl of the electric arcs to the metal wire 2A of the coated wire 2 can be relieved. The relief of the upward crawl of the electric arcs prevents the damage or breakdown of the insulator 2B of the coated wire 2 and can raise the withstand voltage of the coated wire 2, so that the reliability of the bonding technology can be enhanced.

In the present invention, the metal wire 2A of the coated wire 2 can be connected to a voltage higher or lower than the reference potential GND so as to have a plus potential with respect to the arc electrode 10.

The spool 1 round which the coated wire 2 is wound is constructed as illustrated in Fig. 2 and Fig. 6 (an exploded perspective view of essential portions). By way of example, the spool 1 is fabricated by subjecting the surface of a cylindrical member of aluminum metal to an alumite treatment. The alumite treatment is performed in order to raise a mechanical strength and to prevent flaws from developing. This spool 1 has an insulating property because it has been subjected to the alumite treatment as stated above.

The spool 1 is mounted on a spool holder 8, and is attached to the bonding apparatus proper 9 by the rotary shaft 8A of the spool holder 8.

The spool holder 8 is made of, for example, stainless steel in order to have a conductivity in at least a part thereof.

In the bonding apparatus thus constructed, the spool 1 is provided with a connection terminal 1A as shown in Fig. 6 and Fig. 7 (an enlarged perspective view of essential portions). The connection terminal 1A is provided in the shape of a dot on that side face part (flange part) of the spool 1 which comes into contact with the conductive part of the spool holder 8.

As shown in Fig. 7, the connection terminal 1A is so configured that a conductor 1Ab is disposed on an insulator 1Aa and that connecting metal portions 1Ac are disposed on the conductor 1Ab. The insulator 1Aa is made of, for example, polyimide resin so as to exhibit a proper elasticity which ensures the electrical isolation of the connection terminal 1A from the spool 1 and also ensures the touch of the connecting metal portions 1Ac to the spool holder 8. The conductor 1Ab is made of, for example, Cu foil so as to ensure the connection between that one of the connecting metal portions 1Ac which connects the metal wire 2A of the coated wire 2 and the other 1Ac which comes into contact with the spool holder 8. The connecting metal portions 1Ac are

made of a conductive paste, a solder or the like.

The metal wire 2A at the end of the coated wire 2 on the opposite side to the side which is supplied to the bonding space 3, that is, the metal wire 2A at the initial winding end of the coated wire 2 is connected to the connection terminal 1A through a notch which is formed in the side face (flange part) of the spool 1. This metal wire 2A is joined to the connection terminal 1A by the connecting metal portion 1Ac. The insulator 2B on the surface of the metal wire 2A at the initial winding end of the coated wire 2 is removed by heating or chemically. The connection terminal 1A, namely, the metal wire 2A of the coated wire 2 is connected to the reference potential GND through the spool holder 8, the rotary shaft 8A thereof and the apparatus proper 9. This reference potential GND is the same as the reference potential GND of the arcing circuit 11.

In this manner, the spool 1 is furnished with the connection terminal 1A for connecting the metal wire 2A to the reference potential GND, and the metal wire 2A at the initial winding end of the coated wire 2 is joined to this connection terminal, whereby the metal wire 2A can be connected to the reference potential GND through the spool holder 8 etc., so that the metal wire 2A of the coated wire 2 can be reliably connected to the reference potential GND.

Besides, owing to the connection of the metal wire 2A of the coated wire 2 to the reference potential GND, during the formation of the metal ball 2Aa, a sufficient potential difference is secured between the arc electrode 10 and the metal wire 2A of the coated wire 2 on the supply side, and the electric arcs can be favorably struck, so that the metal ball 2Aa can be reliably formed.

Moreover, owing to the connection of the metal wire 2A of the coated wire 2 to the reference potential GND, the stray capacitance of the metal wire 2A of the coated wire 2 can be prevented from being charged up. That is, at the step of first bonding at which the metal ball 2Aa at the supply-side front end of the coated wire 2 is joined to the external terminal 12Aa of the semiconductor chip 12A, charges stored in the stray capacitance can be prevented from flowing into the input/output stage circuit of the semiconductor chip 12A in the form of an excess voltage. Therefore, the electrostatic breakdown of the semiconductor chip is avoidable.

As illustrated in Figs. 1 and 2, the bonding tool 7 is carried by a bonding head (digital bonding head) 14 through a bonding arm 7A. The bonding head 14 is supported on a base 18 through an X-Y table 17. The bonding head 14 is furnished with a second moving mechanism which can move the bonding arm 7A vertically (in the direction of double-headed arrow C) so as to permit the bonding tool 7 to come close to and away from the bonding space 3. The second moving mechanism is principally constructed of a guide member 14A, an arm moving member 14B, a female screw member 14C, a male screw member 14D and a motor 14E. The guide member 14A is so configured as to move the arm moving member 14B in the direction of the arrow C. The motor 14E rotates the male screw member 14D, the female screw member 14C in fit engagement with the male screw member 14D is moved in the direction of the arrow C by the rotation, and the arm moving member 14B is shifted in the direction of the arrow C by the movement.

The bonding arm 7A supported by the arm moving member 14B is adapted to turn about a swivel shaft 14F. The turning of the bonding arm 7A about the swivel shaft 14F is controlled by an elastic member 14G. The control of the turning by the elastic member 14G is so schemed that, when the bonding tool 7 has touched the bonding space 3, this bonding space 3 is prevented from being unnecessarily pressed, whereby the damage or breakdown of the bonding space 3 is avoided.

The wire clamber 6 can clamp the coated wire 2, and is constructed so as to control the supply of the coated wire 2. The wire clamber 6 is mounted on the bonding arm 7A through clamber arms 6A.

The wire guide member 5 is so constructed that the coated wire 2 supplied from the spool 1 is guided to the bonding space 3. This wire guide member 5 is mounted on the clamber arm 6A.

As illustrated in Fig. 1, Fig. 2, Fig. 8 (a sectional view of essential portions) and Fig. 9 (a perspective view of essential portions), an insulator removal torch 15 is disposed near the supply path of the coated wire 2. Concretely, the insulator removal torch 15 is disposed near the supply path of the coated wire 2 between the bonding space 3 and the bonding tool 7.

The insulator removal torch 15 is constructed of a torch proper 15B in the shape of a cylinder which is supplied with a mixed gas G by a mixed-gas supply pipe 15A as shown in Fig. 8, and a heater 15C which is provided near a blowoff outlet for the mixed gas. The torch proper 15B is made of, for example, ceramics, brass or the like. The heater 15C is composed of a heating wire 15Ca which is wound on the torch proper 15B, and a thermal insulator 15Cb which covers the heating wire. This heater 15C is configured so as to heat the mixed gas G (a combustible gas to be described below, contained therein) in order that burning flames may be always blown off from the outlet of the insulator removal torch 15 (a spontaneous firing state in which burning flames do not go out may be kept).

By providing the heater 15C near the blowoff outlet of the insulator removal torch 15 for the combustible gas in this manner, the combustible gas can be reliably burnt, so that the insulator 2B of the coated wire 2 can be reliably decomposed and removed.

The mixed gas G to flow through the torch proper 15B is prepared by mixing the combustible gas, and a temperature controlling gas which lowers the combustion temperature of this combustible gas. As the combustible gas, hydrogen (H_2) is used in the present embodiment. As the temperature controlling gas, nitrogen (N_2) is used in the present embodiment. The burning flames of the combustible gas made up of hydrogen are at a low temperature of about 1300 [$^{\circ}C$], and are formed into a comparatively round shape at the blowoff outlet of the insulator removal torch 15. The temperature controlling gas made up of nitrogen can control (lower) the burning flames of the combustible gas to a low temperature of about 1000 [$^{\circ}C$]. Further, the temperature controlling gas can control the burning flames of the combustible gas into a sharp shape. In order to efficiently lower the temperature of the burning flames, the temperature controlling gas should preferably be supplied into the insulator removal torch 15 in a comparatively cold state.

Alternatively, the insulator removal torch 15 may be supplied with only the combustible gas (for example, H_2) without the feed of the temperature controlling gas.

In this manner, the insulator removal torch 15 is configured so as to blow off the burning flames of the combustible gas from the outlet thereof while controlling the combustion temperature of the combustible gas of the mixed gas G by the use of the temperature controlling gas. As illustrated in Figs. 8 and 9, the burning flames from the blowoff outlet of the insulator removal torch 15 are adapted to decompose and remove the insulator 2B of the coated wire 2. They are sharply blown off in a direction which is substantially orthogonal to the supply path of the coated wire 2. The insulator 2B decomposed and removed is imbibed and expelled by a suction duct 16 which is disposed at a position confronting the blowoff outlet of the insulator removal torch 15 with the coated wire 2 intervening therebetween.

The insulator removal torch 15 is attached to a third moving mechanism which traverses the supply path of the coated wire 2 in the direction of arrows D (refer to Fig. 9). The third moving mechanism is constructed of a rotary member 15E which turns the torch proper 15B about a pin 15D, and a pressure solenoid 15F which turns the rotary member 15E in the direction of double-headed arrow E. This third moving mechanism is configured so that the coated wire 2 may be traversed at a predetermined speed and that the burning flames from the outlet of the insulator removal torch 15 may be blown against the side of the insulator 2B confronting the outlet and the rear side thereof. That is, the third moving mechanism is configured so that the burning flames from the insulator removal torch 15 may turn to the rear side of the insulator 2B of the coated wire 2 more reliably. The operation of the insulator removal torch 15 based on the third moving mechanism is set so that the coated wire 2 may be traversed once or more times.

As illustrated in Figs. 8 and 9, the third moving mechanism is attached to a fourth moving mechanism which moves the third one in the direction of double-headed arrow F (substantially the same direction as the supply direction of the coated wire 2). The fourth moving mechanism is principally constructed of a movable bed 15G, a guide member 15H, a male screw member 15I, and a motor 15J. The movable bed 15G has the third moving mechanism (the insulator removal torch 15) mounted thereon, and is adapted to move in the direction of double-headed arrow F along the guide member 15H. The movement of the movable bed 15G is executed in such a way that a female screw portion (not shown) formed in this bed is held in fit engagement with the male screw member 15I and that the male screw member 15I is rotated by the motor 15J.

The fourth moving mechanism is configured so as to set the insulator removal torch 15 at the bonding part of the coated wire 2. That is, the fourth moving mechanism is configured so as to set the insulator removal torch 15 to the vicinity of that position of the coated wire 2 which corresponds to the bonding part to be joined with the inner lead part of the lead 12D and the bonding part to be joined with the external terminal 12Aa of the semiconductor chip 12A at a bonding step next that of the first-mentioned bonding part. The insulator removal torch 15 set at the position is adapted to remove the insulator 2B of both the bonding parts of the coated wire 2 at an identical step by the use of the burning flames.

As indicated in Figs. 10 and 11 (graphs each showing the relationship between the melting point of the metal wire of the coated wire and the decomposition temperature of the insulator thereof), the insulator removal torch 15 constructed as stated above can reliably remove the insulator 2B without damaging the metal wire 2A of the coated wire 2. Experimental results in Figs. 10 and 11 were obtained by differential thermal analyses.

Fig. 10 is the graph showing the relationship between the melting point M of the metal wire 2A made of gold (Au) and the decomposition temperature of the insulator 2B made of polyurethane resin. The axis of abscissas represents the temperature T [$^{\circ}C$], while the axis of ordinates represents the decomposition residue weight W [%] of the insulator 2B. As shown in Fig. 10, the decomposition and removal of the insulator 2B of the coated wire 2 is most suitably carried out within a range of temperatures which are nearly equal to or lower than the melting point of the metal wire 2A and at which the insulator 2B can be reliably decomposed and removed, in other words, within a range of low temperatures of approximately 600 - 950 [$^{\circ}C$] which form a temperature range denoted by letter R in Fig. 10. Since the burning flames from the blowoff outlet of the insulator removal torch 15 is controlled to the low temperature of approximately 1000 [$^{\circ}C$] as stated be-

fore, the insulator 2B of the coated wire 2 can be decomposed and removed under the optimum condition.

By way of example, Table 1 to be mentioned later lists various conditions in the case of using a coated wire 2 whose metal wire 2A has a diameter of 30 [μm].

On the other hand, Fig. 11 is the graph showing the relationship between the melting point M of the metal wire 2A made of gold (Au) and the decomposition temperature of the insulator 2B made of polyimide resin. As shown in Fig. 11, the decomposition and removal of the insulator 2B of the coated wire 2 is most suitably carried out within a range of low temperatures of approximately 800 - 950 [$^{\circ}\text{C}$].

Meanwhile, as illustrated in Fig. 12 (a graph showing the relationship between a voltage V applied to the heating wire of the heater and the temperature T of the burning flames blown off from the outlet), the insulator removal torch 15 is so constructed that the temperature T of the burning flames to be blown off from the outlet can be controlled by the applied voltage V of the heating wire 15Ca of the heater 15. In Fig. 12, the axis of abscissas represents the voltage V [V] applied to the heating wire 15Ca, while the axis of ordinates represents the temperature T of the burning flames. For reference, the temperature T_H of the flames of oxyhydrogen (the temperature of the burning flames of a mixed gas consisting of hydrogen gas and oxygen gas) is indicated in Fig. 12. The oxyhydrogen flames are at a high temperature of approximately 3400 [$^{\circ}\text{C}$], so that when they are used for the removal of the insulator 2B of the coated wire 2, the metal wire 2A as well as the insulator 2B is melted and damaged.

Next, the ball-bonding method of the present embodiment will be briefly described.

First, as shown in Fig. 5, the arc electrode 10 is brought near to that supply-side front end part of the coated wire 2 from which the insulator 2B has been removed to denude the surface of the metal wire 2A beforehand, and the electric arcs are struck to form the metal ball 2Aa.

Secondly, the bonding tool 7 is brought near to the bonding space 3, and the metal ball 2Aa is bonded to the external terminal 12Aa of the semiconductor chip 12A (first bonding).

Subsequently, the bonding tool 7 is raised in the direction of the arrow C up to an appropriate position so as to come away from the external terminal 12Aa.

Subsequently, the insulator removal torch 15 is set at the position near the bonding part (second bonding) of the coated wire 2. Then, the burning flames which are blown off from the outlet of the insulator removal torch 15 at all times traverse the coated wire 2, thereby to decompose and remove the insulator 2 of the bonding part of the coated wire 2 and to denude the surface of the metal wire 2A as illustrated in Figs. 8 and 9.

In this manner, the mixed gas consisting of the combustible gas and the temperature controlling gas is prepared, and the combustion flames obtained by burning the combustible gas of the mixed gas are used for removing the insulator 2B of the bonding part of the coated wire 2 and denuding the surface of the metal wire 2A, whereby the combustion flames which do not impose any damage or breakdown on the metal wire 2A can be turned round substantially the whole area of the bonding part of the coated wire 2, and hence, the insulator 2B of the coated wire 2 can be reliably removed. That is, the removal of the insulator 2B of the coated wire 2 by the burning flames of the lower temperature has the feature of imposing no damage on the metal wire 2A when compared with the removal thereof by the oxyhydrogen flames, and it has the feature of being capable of reliably removing the insulator on the basis of the turning-round of the burning flames when compared with the removal thereof by the laser beam.

At the next step, the bonding tool 7 is lowered to the position from which the insulator 2B has been removed to denude the metal wire 2A. As illustrated by phantom lines in Fig. 8, the bonding tool 7 is brought near to the inner lead part, whereby the other end of the coated wire 2 at which the metal wire 2A is denuded is bonded to the inner lead part (the second bonding).

Subsequently, the bonding tool 7 is brought away, and the coated wire 2 is cut, whereby the bonding process is completed as shown in Fig. 4.

Since the insulator 2B of the coated wire 2 can be reliably removed in the foregoing way, the metal wire 2A of the coated wire 2 and the bonding space 3 (the external terminal 12Aa or the inner lead part) can be reliably joined, and bonding defects can be lessened.

Incidentally, although Embodiment 1 has bonded the coated wire 2 and the bonding space 3 by the use of the ball-bonding technology, the present invention can bond them by the use of ultrasonic bonding technology.

Besides, the present invention can use carbonic acid gas (CO) as the combustible gas of the mixed gas and can use argon (Ar) or helium (He) as the temperature controlling gas.

Besides, the present invention is applicable to the wire bonding techniques of a ceramic-encapsulated semiconductor device, an electron device in which a plurality of semiconductor chips are packaged on a wiring circuit board, etc.

Besides, the present invention may be so constructed that the combustible gas is caused to flow through the torch proper 15B of the insulator removal torch 15 and is burnt at the blowoff outlet, while the temperature

controlling gas is blown off near the outlet.

Further, as the wire bonding system, the present invention can adopt the thermocompression system or/and the ultrasonic vibration system under the optimum conditions for the specifications of the coated wire and the device to be subjected to the wire bonding.

Embodiment 2:

Embodiment 2 is another embodiment of the present invention which alters the configuration of the arc electrode for forming the metal ball in the bonding apparatus of Embodiment 1.

Though not shown in the drawings, the bonding apparatus which is Embodiment 2 of the present invention is so constructed that, in forming the metal ball 2Aa at the front end of the coated wire 2 by means of the arc electrode 10 shown in Fig. 5, this metal ball 2Aa is shielded from an outer atmosphere by an inert gas.

The inert gas is blasted from a shield-gas supply nozzle for supplying it, the nozzle being disposed near the interspace between the arc electrode 10 and the metal wire 2A at the front end of the coated wire 2. Alternatively, the arc electrode 10 may be provided with a cylindrical member into which the metal wire 2A at the front end of the coated wire 2 can be inserted, whereupon the inert gas is blasted into the cylindrical member. As the inert gas, argon (Ar) or helium (He) is used.

In this manner, in forming the metal ball 2Aa, the surrounding region thereof is shielded from the outer atmosphere by the inert gas, whereby in the case of making the insulator 2B of the coated wire 2 out of a resin, the melting and rising or shrinking of the insulator 2B is mitigated, and the chemical reaction thereof with the outer atmosphere can be prevented, so that the metal ball 2Aa can be formed to be favorable. Especially in the case of making the metal wire 2A of the coated wire 2 out of copper (Cu), the chemical reaction thereof with the outer atmosphere can be prevented, and the formation of an oxide film on the surface of the metal ball 2Aa can be avoided.

Embodiment 3:

Embodiment 3 is another embodiment of the present invention in which, in the bonding apparatus, the metal ball is formed by a combustion torch.

This embodiment 3 is so constructed that, in the ball-bonding technology, the metal ball 2Aa at the front end of the coated wire 2 is formed by the insulator removal torch 15 for removing the insulator 2B as stated before. In other words, the setup of the arc electrode 10 and the arcing circuit 11 can be dispensed with.

Apart from the insulator removal torch 15, an oxyhydrogen flame torch may be disposed as the torch for forming the metal ball 2Aa.

More specifically, a bonding process proceeds as follows:

First, using the burning flames of the insulator removal torch 15 or the oxyhydrogen flame torch, the metal ball 2Aa is formed at the supply-side front end of the coated wire 2.

Secondly, the first bonding is carried out.

Subsequently, using the burning flames of the insulator removal torch 15, the insulator 2B at the bonding parts of the coated wire 2 (the second bonding part, and the first bonding part at the next step) is removed to denude the surface of the metal wire 2A.

Subsequently, the second bonding is carried out.

Next, likewise to the foregoing, the metal ball 2Aa is formed at the supply-side front end of the coated wire 2 by the use of the burning flames of the insulator removal torch 15 or the oxyhydrogen flame torch. In the case of forming the metal ball 2Aa by means of the insulator removal torch 15, when the melting point of the metal wire 2A of the coated wire 2 is not reached, the mixing ratio of the gaseous mixture is changed, or/and the moving speed of the burning flames to traverse the coated wire 2 is controlled.

In this manner, the metal wire 2A of the coated wire 2 from which the insulator 2B has been removed is formed into the metal ball 2Aa by the use of the burning flames mentioned above or burning flames formed by the combustion of any other mixed gas, whereby the metal ball 2Aa of the coated wire 2 is formed by the burning flames, so that the arc electrode 10 and the arcing circuit 11 described in Embodiments 1 and 2 can be abolished.

Embodiment 4:

Embodiment 4 is another embodiment of the present invention which alters the configuration of the insulator removal torch in the bonding apparatus.

Though not shown in the drawings, Embodiment 4 is so constructed that the heater 15C of the insulator

removal torch 15 described in each of Embodiments 1, 2 and 3 is removed and that the size (diameter) of the blowoff outlet of the insulator removal torch 15 for the combustible gas is made smaller than the bore of the torch proper 15B. With the insulator removal torch 15 thus constructed, the heat capacity of the burning flames of the combustible gas to be blown off from the outlet can be decreased. The size of the blowoff outlet is set within a range from the minimum value of 75 [μm] based on a machining limit, to the maximum value of 125 [μm] for the decrease of the heat capacity of the burning flames.

Since the insulator removal torch 15 thus constructed can make the heat capacity smaller, it can use the combustible gas (for example, H_2) only, the combustible gas and the temperature controlling gas (for example, N_2) for lowering the temperature of the burning flames of the combustible gas, or a temperature controlling gas (for example, a slight amount of O_2) for raising the temperature of the burning flames of the combustible gas. By way of example, Table 2 to be mentioned later lists various conditions for removing the insulator 2B of the coated wire 2.

In this manner, the heat capacity of the burning flames at the blowoff outlet of the combustible gas can be decreased by making the size of the outlet of the insulator removal torch 15 smaller, so that the transfer of heat to the bonding tool 7 located near the insulator removal torch 15 is diminished, and the insulator 2B of the coated wire 2 to be supplied can be prevented from damaging or breaking down.

[Table 1]

1	Length of Burning flames	7 [mm]
2	Combustible gas H_2	0.82 [lit./min.]
3	Temperature controlling gas N_2	0.15 [lit./min.]
4	Bore of Torch proper	0.5 [mm]
5	Velocity of flow of Mixed gas	85 [m/sec.]
6	Temperature of Blowoff outlet	1050 [$^{\circ}\text{C}$]
7	Temperature of Burning flames at a position 4 mm distant from Outlet	850 [$^{\circ}\text{C}$]
8	Resistance of Heating wire	4.5 [Ω]
9	Voltage applied to Heating wire	20 [V]
10	Time in which Coated wire is Traversed	0.01 - 0.05 [sec.]

[Table 2]

1	Length of Burning flames	3.5 [mm]
2	Combustible gas H ₂	0.01 - 0.15 [lit./min.]
3	Bore of Torch proper	0.5 [mm]
4	Diameter of Blowoff outlet	35 - 150 [μ m]
5	Velocity of flow of Mixed gas	200 - 300 [m/sec.]
6	Temperature of Blowoff outlet	1300 [°C]

(to be continued)

7	Temperature of Burning flames at a position 4 mm distant from Outlet	1300 [°C]
8	Time in which Coated wire is Traversed	0.01 - 0.05 [sec.]

Embodiment 5:

As described above, the technique disclosed in Embodiments 1 - 4 is effective as the technique for removing the insulator of the coated wire. This technique consists in that the burning flames from the insulator removal torch are blown against the bonding part of the coated wire, thereby to remove the insulator at the part. The burning flames are formed by the mixed gas which consists of hydrogen gas for combustion and temperature-controlling nitrogen gas for lowering the combustion temperature of the hydrogen gas. The insulator removal torch is so constructed that the insulator on the rear end side of the coated wire to be joined with the lead and the insulator on the front end side of the coated wire (bonding part) to be joined with the external terminal at the next step are removed at a time. This insulator removal torch is moved to the bonding part (the part where the insulator is to be removed) of the coated wire by the moving mechanisms and the controllers. The removal of the insulator of the coated wire employing this technique does not damage the metal wire of the coated wire, and can turn the burning flames round the whole area of the bonding part to completely remove the insulator. Therefore, it has the feature that a bonding defect (inferior continuity) attributed to the remaining of the insulator can be prevented.

The inventors, however, have found out that the following problems are involved in the technique stated above:

As described before, the removal of the insulator of the coated wire is executed by the insulator removal torch. This insulator removal torch is moved near to the bonding parts of the coated wire corresponding to the changes of the distances between the external terminals of the semiconductor chip and the leads, at the respective bonding steps. In consequence, not only the construction of the insulator removal torch, but also that of the bonding apparatus becomes somewhat complicated because the moving mechanisms for the torch and the controllers for complicately controlling the moving mechanisms are necessitated.

In addition, the ball at the supply-side front end of the coated wire is formed by bringing the electric torch near to the front end and striking electric arcs across the metal wire and the electric torch. After being formed, the ball on the front end side of the coated wire is joined to the external terminal of the semiconductor chip. In this regard, it has been acknowledged by the inventors that, in forming the ball on the front end side of the

coated wire, heat attendant upon the generation of the electric arcs incurs the phenomenon in which the insulator melts and rises or shrinks from the front end side to the rear end side of the coated wire. The shrinkable melting of the insulator forms insulator globes (the bulk of the insulator) in the coated wire. The insulator globes grow to be larger than the diameter of the hole of the bonding tool for guiding the coated wire. Consequently, in a case where the ball is drawn toward the pressing face of the bonding tool after the formation thereof on the front end side of the coated wire, a catch develops between the coated wire and the guide hole of the bonding tool. For this reason, the subsequent step of joining the ball to the external terminal of the semiconductor chip by means of the pressing face of the bonding tool becomes impossible, and a bonding defect arises.

Embodiment 5 to be detailed in this section solves the problems explained above.

Now, this embodiment will be described in detail.

A ball-bonding (wire bonding) apparatus which is Embodiment 5 of the present invention is illustrated as a schematic constructional view in Fig. 13 and as a perspective view of essential portions in Fig. 14.

As shown in Fig. 13, the ball-bonding apparatus is so constructed that a coated wire 102 wound round a spool 101 is supplied to a bonding space 103. The supply of the coated wire 102 to the bonding space 103 is performed through a tensioner 104, a wire guide member 105, a wire clasper 106 and a bonding tool (capillary) 107.

In the bonding space 103, a resin-encapsulated type semiconductor device 120 before resin encapsulation to be constructed as shown in Fig. 15 (a sectional view) and Fig. 16 (an enlarged sectional view of essential portions) is arranged. The resin-encapsulated semiconductor device 120 is so constructed that a semiconductor chip 120A placed on a tab portion 120C through a connecting metal film 120B and the inner lead parts of leads 120D are encapsulated by a resin mold member 120E. The semiconductor chip 120A and the lead 120D are connected by the coated wire 102. As shown in Fig. 16, one end of the coated wire 102 is joined to an external terminal (bonding pad) 120Aa which is exposed through an opening provided in the passivation film 120Ab of the semiconductor chip 120A. The other end of the coated wire 102 is joined to the inner lead part of the lead 120D. The outer lead part of the lead 120D is formed so as to protrude outside the resin mold member 120E. The resin-encapsulated type semiconductor device 120 before the resin encapsulation step is supported on the semiconductor device bed (table for setting the semiconductor device) 113 of the bonding apparatus as depicted in Fig. 13.

As its structure is shown in detail in Fig. 16, the coated wire 102 is so constructed that the surface of a metal wire 102A is coated with an insulator 102B. The metal wire 102A is made of gold (Au) in the present embodiment. Alternatively, the metal wire 102A is made of copper (Cu), aluminum (Al) or the like. The insulator 102B is formed of a polyurethane resin film or a polyimide resin film in the present embodiment. Alternatively, the insulator 102B is formed of a resin film such as ester imide resin film or ester amide resin film, or a metal oxide film (of CuO, Cu₂O or Al₂O₃).

Joined to the external terminal 120Aa of the semiconductor chip 120A is a metal ball 102Aa which is formed of the metal wire 102A denuded by removing the insulator 102B on one end side of the coated wire 102. The metal ball 102Aa is configured with a diameter which is, for example, about 2 - 3 times as large as the diameter of the metal wire 102A. Joined to the inner lead part of the lead 120D is the metal wire 102A on the other end side of the coated wire 102 as denuded by destroying the insulator 102B on the other end side of the coated wire 102 being a joint part. That is, on the other end side of the coated wire 102, only the insulator 102B corresponding substantially to the joint part with the lead 120D is removed, and the insulator 102B in the other part is left behind. As will be described later, the destruction of the insulator 102B on the other end side of the coated wire 102 can be effected by ultrasonic vibrations, appropriate pressure application and appropriate heating (energy) which are afforded by the bonding tool 107.

In this manner, in the resin-encapsulated semiconductor device 120 which uses the coated wire 102, the metal ball 102Aa formed of the metal wire 102A on one end side of the coated wire 102 is joined to the external terminal 120Aa of the semiconductor chip 120A, and the metal wire 102A on the other end side of the coated wire 102 with the insulator 102B of the contact part destroyed is joined to the lead 120D, whereby the external terminal 120Aa of the semiconductor chip 120A and the metal wire 102A of the coated wire 102 have their contact area increased owing to the ball-bonding system employing the metal ball 102Aa larger in size, in comparison with a contact area in a system connecting a bonding wire through ultrasonic vibrations, and the bondability between the two can be enhanced. Simultaneously, the other end side of the coated wire 102 except the part to be joined with the lead 120D is kept coated with the insulator 102B, and the short-circuiting between the other end side of this piece of coated wire 102 and that of another adjacent piece of coated wire 102 can be mitigated, so that the intervals of the leads 120D can be shortened to achieve increase in the number of terminals (pins) of the resin-encapsulated semiconductor device 120.

As illustrated in Figs. 13 and 14, the bonding tool 107 and the front end part of the coated wire 102 in the supply direction thereof (the part where the metal ball 102Aa is to be formed) are arranged so as to be con-

sealed by a cover member 110A when the metal ball 102Aa is to be formed. The cover member 110A is constructed so as to move and turn in the direction of double-headed arrow A indicated in Fig. 14. That is, the cover member 110A is so constructed that, at the step of forming the metal ball 102Aa, the bonding tool 107 is inserted therewith through a tool insertion port 110B by the turning motion in the direction of the arrow A and is covered therewith. This cover member 110A is configured as shown in Fig. 17 (a partial sectional view showing a concrete construction, and corresponding to a section taken along cutting-plane line V - V in Fig. 18), Fig. 18 (a plan view seen in the direction of arrow VI in Fig. 17) and Fig. 19 (a sectional view taken along cutting-plane line VII - VII in Fig. 18). As will be stated later, the cover member 110A is so set up that, at the step of forming the metal ball 102Aa, the insulator 102B does not scatter to the bonding space 103 due to the blowing-away of the insulator 102B which melts and rises or shrinks. Besides, the cover member 110A is set up so as to facilitate the retention of a cover gas atmosphere (a shield gas atmosphere) for the prevention of oxidation in a case where the metal wire 102A of the coated wire 102 is made of a material easy of oxidation such as Cu or Al. The cover member 110A is made of, for example, stainless steel. Alternatively, the cover member 110A may be made of a transparent glass material so as to permit an operator to acknowledge the state of the formation of the metal ball 102Aa of the coated wire 102, etc.

An electric torch (arc electrode) 110D is disposed at the bottom part of the cover member 110A as shown in Figs. 13, 14, 17 and 19. As illustrated in Fig. 20 (a model-like constructional view for elucidating the principle of forming the metal ball), the electric torch 110D is constructed so as to come near to the metal wire 102A at the supply-side front end of the coated wire 102 and to strike electric arcs across it and the metal wire, thereby to form the metal ball 102Aa. This electric torch 110D is made of, for example, tungsten which endures high temperatures.

The electric torch 110D is connected to an arcing unit 112 through that suction pipe 110E of a suction unit 111 which is made of a conductive material. The suction pipe 110E is made of, for example, stainless steel and has the electric torch 110D fastened thereto through a bonding metal layer of Ag-Cu brazing material or the like. This suction pipe 110E is fastened to the cover member 110A through a clamp member 110F. That is, the electric torch 110D as well as the suction pipe 110E and the cover member 110A are unitarily constructed.

The electric torch 110D can move in the direction of the arrow A indicated in Fig. 14 so as to come near to the supply-side front end of the coated wire 102 when the metal ball 102Aa is formed as stated before and to come away from the supply path of the coated wire 102 during the bonding process. A moving mechanism for moving the electric torch 110D is principally constructed of a support member 110G which supports the electric torch 110D through the suction pipe 110E as well as an insulating member 110H, a crank shaft 110I which turns the support member 110G in the direction of the arrow A, and a drive source 110K which rotates the crank shaft 110I. The rotation of the crank shaft 110I is executed by the movement of the shaft 110J of the drive source 110K in the direction of double-headed arrow B, the shaft 110J being coupled to the crank portion of the crank shaft 110I. The drive source 110K is constructed of, for example, an electric solenoid. Though not illustratively clarified, the crank shaft 110I is rotatably supported on a bonding apparatus proper. Incidentally, the movement of the electric torch 110D and that of the cover member 110A are substantially the same because both these constituents are unitarily constructed.

As shown in Fig. 14, the arcing unit 112 is principally constructed of a capacitor C₁, a storage capacitor C₂, an arcing thyristor D which is actuated by a trigger, and a resistor R. A d.c. power source DC is arranged so as to feed a voltage of negative polarity at, for example, approximately -1000 -3000 [V]. The d.c. power source DC is connected to the electric torch 110D through the thyristor D, the resistor R, etc. A reference potential GND is, for example, the ground potential (= 0 [V]). Letter V indicates a voltmeter, and letter A an ammeter. As will be described in detail later, the metal wire 102A of the coated wire 102 is connected to the reference potential GND at its end part wound round the spool 101. As a result, in the case of forming the metal ball 102Aa at the front end of the coated wire 102 by the use of the electric torch 110D, it is possible to set the electric torch 110D at a negative potential (-) and the metal wire 102A of the front end of the coated wire 102 in the supply direction thereof at a positive potential (+) as illustrated in Figs. 13, 14 and 20.

In the bonding apparatus wherein, in this manner, the electric arcs are struck across the metal wire 102A at the front end of the coated wire 102 and the arc electrode 110D so as to form the metal ball 102Aa at the front end of the coated wire 102, the metal wire 102A of the coated wire 102 is connected to the positive potential (+), and the electric torch 110D is connected to the negative potential (-), whereby the appearing position of the electric arcs struck across the metal wire 102A of the coated wire 102 and the electric torch 110D can be stabilized more than in case of the opposite polarity, and hence, the upward crawl of the electric arcs toward the rear end side of the metal wire 102A of the coated wire 102 can be relieved. The relief of the upward crawl of the electric arcs can reduce the shrinkable melting of the insulator 102B of the coated wire 102 and prevent the appearance of insulator globes.

In the present invention, the metal wire 102A of the coated wire 102 may well be connected to a voltage

higher or lower than the reference potential GND so as to have a plus potential with respect to the electric torch 110D.

The spool 101 round which the coated wire 102 is wound is constructed as illustrated in Fig. 14 and Fig. 21 (an exploded perspective view of essential portions). By way of example, the spool 101 is fabricated by subjecting the surface of a cylindrical member of aluminum metal to an alumite treatment. The alumite treatment is performed in order to raise a mechanical strength and to prevent flaws from developing. This spool 101 has an insulating property because it has been subjected to the alumite treatment as stated above.

The spool 101 is mounted on a spool holder 108, and is attached to the bonding apparatus proper 109 by the rotary shaft 108A of the spool holder 108.

The spool holder 108 is made of, for example, stainless steel in order to have a conductivity in at least a part thereof.

The spool 101 is provided with a connection terminal 101A as shown in Fig. 21 and Fig. 22 (an enlarged perspective view of essential portions). The connection terminal 101A is provided in the shape of a dot on that side face part (flange part) of the spool 101 which comes into contact with the conductive part of the spool holder 108.

As shown in Fig. 22, the connection terminal 101A is so configured that a conductor 101Ab is disposed on an insulator 101Aa and that connecting metal portions 101Ac are disposed on the conductor 101Ab. The insulator 101Aa is made of, for example, polyimide resin so as to exhibit a proper elasticity which ensures the electrical isolation between the conductor 101Ab and the spool 101 and also ensures the touch of the connecting metal portions 101Ac to the spool holder 108. The conductor 101Ab is formed of, for example, Cu foil so as to ensure the connection between that one of the connecting metal portions 101Ac which connects the metal wire 102A of the coated wire 102 and the other 101Ac which comes into contact with the spool holder 108. The connecting metal portions 101Ac are made of a conductive paste, a solder or the like.

The metal wire 102A at the end of the coated wire 102 on the opposite side to the side which is supplied to the bonding space 103, that is, the metal wire 102A at the initial winding end of the coated wire 102 is connected to the connection terminal 101A through a notch which is formed in the side face (flange part) of the spool 101. This metal wire 102A is joined to the connection terminal 101A by the connecting metal portion 101Ac. The insulator 102B on the surface of the metal wire 102A at the initial winding end of the coated wire 102 is removed by heating or chemically. The connection terminal 101A, namely, the metal wire 102A of the coated wire 102 is connected to the reference potential GND through the spool holder 108, the rotary shaft 108 thereof and the apparatus proper 109. This reference potential GND is the same as the reference potential GND of the arcing unit 112.

In this manner, the spool 101 is furnished with the connection terminal 101A for connecting the metal wire 102A to the reference potential GND, and the metal wire 102A at the initial winding end of the coated wire 102 is joined to this connection terminal, whereby the metal wire 102A can be connected to the reference potential GND through the spool holder 108 etc., so that the metal wire 102A of the coated wire 102 can be reliably connected to the reference potential GND.

Besides, owing to the connection of the metal wire 102A of the coated wire 102 to the reference potential GND, during the formation of the metal ball 102Aa, a sufficient potential difference is secured between the electric torch 110D and the metal wire 102A of the coated wire 102 on the supply side, and the electric arcs can be favorably struck, so that the metal ball 102Aa can be reliably formed.

As illustrated in Figs. 13 and 14, the bonding tool 107 is carried by a bonding head (digital bonding head) 114 through a bonding arm 107A. Though not shown, an ultrasonic vibrator is built in the bonding arm 107A, and it is adapted to vibrate the bonding tool 107 ultrasonically. As the wire bonding system, accordingly, the thermocompression system or/and the ultrasonic vibration system can be adopted under the optimum conditions for the specifications of the coated wire and the device to be subjected to the wire bonding. The bonding head 114 is supported on a base 118 through an X-Y table 117. The bonding head 114 is furnished with a moving mechanism which can move the bonding arm 107A vertically (in the direction of double-headed arrow C) so as to permit the bonding tool 107 to come close to and away from the bonding space 103. This moving mechanism is principally constructed of a guide member 114A, an arm moving member 114B, a female screw member 114C, a male screw member 114D and a motor 114E. The guide member 114A is so configured as to move the arm moving member 114B in the direction of the arrow C. The motor 114E rotates the male screw member 114D, the female screw member 114C in fit engagement with the male screw member 114D is moved in the direction of the arrow C by the rotation, and the arm moving member 114B is shifted in the direction of the arrow C by the movement.

The bonding arm 107A supported by the arm moving member 114B is adapted to turn about a swivel shaft 114F. The turning of the bonding arm 107A about the swivel shaft 114F is controlled by an elastic member 114G. The control of the turning by the elastic member 114G is so schemed that, when the bonding tool 107

has touched the bonding space 103, this bonding space 103 is prevented from being unnecessarily pressed, whereby the damage or breakdown of the bonding space 103 is avoided.

The wire clasper 106 clamps the coated wire 102, and is constructed so as to control the supply of the coated wire 102. The wire clasper 106 is mounted on the bonding arm 107A through clasper arms 106A.

5 The wire guide member 105 is so constructed that the coated wire 102 supplied from the spool 101 is guided to the bonding space 103. This wire guide member 105 is mounted on the clasper arm 106A.

Near the front end of the coated wire 102 in the supply direction thereof and near the supply path of the coated wire 102 between the bonding tool 107 and the bonding space 103, the fluid blast nozzles 110C of a fluid blast equipment 119 are disposed as shown in Figs. 13, 14, 17 and 20. The fluid blast nozzles 110C are so constructed that, when the metal ball 102Aa is formed of the metal wire 102A at the front end of the coated wire 102 in the supply direction thereof, a fluid or gas from the fluid blast equipment 119 is blasted against the area of the formation (the metal wire 102A and the insulator 102B). As illustrated in Fig. 20, the gas which is blasted from the fluid blast nozzles 110C is adapted to blow away (102Ba) the insulator 102B which is melted and raised or shrunk by heat the electric arcs generate in the case where the metal ball 102Aa is formed of the metal wire 102A at the front end of the coated wire 102.

The fluid blast nozzles 110C may basically blast the gas against the front end part of the bonding tool 107, namely, the front end part of the coated wire 102 as stated above, and they are mounted on the cover member 110A in the present embodiment. As their concrete structure is shown in Fig. 14 and Figs. 17 to 19, the fluid blast nozzles 110C are configured so as to blast the gas from the rear end side toward the front end side of the coated wire 102 for the purpose of diminishing the shrinkable melting of the insulator 102B. Incidentally, it is more preferable that the fluid blast nozzles 110C are not mounted on the bonding tool 107. In a case where the fluid blast nozzles 110C are mounted on the bonding tool 107, the weight of the bonding tool 107 increases to heighten the load of the ultrasonic vibrations thereof, and hence, the bondability of the joint part degrades.

A gas such as N₂, H₂, He, Ar or air is used as the fluid. As illustrated in Fig. 20, it is supplied from the fluid blast equipment (fluid source) 119 to the fluid blast nozzles 110C through a cooler 119A, a flowmeter 119B and a fluid conveyance pipe 119C.

The cooler 119A is configured so as to positively cool the gas below the normal temperature. By way of example, it is constructed of an electronic cooler which utilizes the Peltier effect. Though illustrated in simplified fashion in Fig. 20, the fluid conveyance pipe 119C is so constructed that at least its section between the cooler 119A and a supply port for the fluid blast nozzles 110C is covered with a thermal insulator 119D. That is, the thermal insulator 119D is arranged in order that the temperature of the gas cooled by the cooler 119A may not change during the conveyance of the gas through the fluid conveyance pipe 119C (that the cooling efficiency may be heightened).

As an alternative example of the cooler, a product "COLDER" manufactured by SANWA ENTERPRISES Co., Ltd. may be used. This product "COLDER" is a device which generates air of very low temperature on the basis of the principle of a vortex, and with which the temperature of the cold air and the rate of discharge of the cold air can be regulated by simple operations. This device "COLDER" can generate the very cold air at -50 °C merely by connecting compressed air at an incoming air temperature of +15 °C under an incoming air pressure of 7 kg/cm². It is compact, and is smaller in size than the electronic cooler utilizing the Peltier effect.

40 Besides, when the device "COLDER" is employed together with the cooler utilizing the Peltier effect, there is the effect that the whole cooler as described above can be made smaller in size and lighter in weight.

Meanwhile, the suction pipe 110E coupled to the suction unit 111 is disposed at the position which is close to the front end of the coated wire 102 in the supply direction thereof and which opposes to the fluid blast nozzles 110C with the melted and shrunk part of the insulator 102B of the coated wire 102 intervenign therebetween. Although this suction pipe 110E is used also as the electric conductor for connecting the electric torch 110D and the arcing unit 112 as stated before, it is principally intended to imbibe the melted and shrunk insulator 102Ba of the coated wire 102 blown away by the fluid blast nozzles 110C. The insulator 102Ba imbibed by the suction pipe 110E is drawn by the suction unit 111.

Next, the ball-bonding method of the present embodiment will be briefly explained.

50 First, as illustrated in Figs. 13, 14, 17 and 20, the bonding tool 107 and the front end part of the coated wire 102 in the supply direction thereof as protruded on the side of the pressing face of the bonding tool are concealed by the cover member 110A. The concealment is attained in such a way that the cover member 110A is moved in the direction of the arrow A by the moving mechanism which is actuated by the drive source 110K. Besides, the concealment by the cover member 110A can arrange both the electric torch 110D and the fluid blast nozzles 110C near the front end of the coated wire 102.

Secondly, as illustrated in Fig. 20, the electric arcs are struck across the electric torch 110D and the metal wire 102A at the front end of the coated wire 102 in the supply direction thereof so as to form the metal ball 102Aa out of the metal wire 102A. The heat of the electric arcs for forming the metal ball 102Aa melts and

raises or shrinks the insulator 102B at the front end of the coated wire 102 in the supply direction thereof. That is, the insulator 102B at the front end of the coated wire 102 in the supply direction thereof is removed to denude the metal wire 102A.

The metal ball 102Aa is formed in a short time as illustrated in Fig. 23 (a graph of the relationship between the magnitude of energy of the electric arcs and the magnitude of shrinkable melting of the insulator). In this figure, the axis of abscissas represents the electric discharge time T_e [ms] of the electric arcs, while the axes of ordinates represent the magnitude of current I_e [mA] and the magnitude of shrinkable melting L [mm] of the insulator 102B of the coated wire 102. Data mentioned in Fig. 23 indicates the magnitude of shrinkable melting L [mm] of the insulator (polyurethane resin) 102B required for forming the metal ball 102Aa of the coated wire 102 into a diameter ϕ_b of 60 [μ m] in a case where the ambient temperature is the normal temperature of 25 [$^{\circ}$ C], where the diameter ϕ_w of the metal wire (Au) 102A of the coated wire 102 is 25 [μ m] and where the voltage [V] is 1400 [V] or 2200 [V]. As illustrated in the graph, when the metal ball 102Aa is formed in a shorter time and at higher energy (in a region in which both the current and the voltage are higher), the magnitude of shrinkable melting of the insulator 102B of the coated wire 102 decreases more (as indicated by a thick solid line). As the result of a fundamental experiment by the inventors, in a highly-packaged resin-encapsulated semiconductor device 120 in which the number of leads 102D, i. e., the number of pins was about 100, the metal ball 102Aa could be formed in a short time of 100 - 1000 [μ s], and the magnitude of shrinkable melting L of the insulator 102B of the coated wire 102 could be suppressed within a range of small values of 0.2 - 0.4 [mm]. The magnitude of shrinkable melting L of the insulator is stipulated by the requisites that the coated wire does not continue to the adjacent wire due to the melted and shrunk part of the coating, and that the outer part of the semiconductor pellet do not touch or do not fall into a continuous state due to the melted and shrunk part of the coating. Forming the metal ball 102Aa in the shorter time and at the higher energy in this manner, can be realized by stabilizing the generation of the electric arcs as described before, namely, by setting the electric torch 110D at the minus potential (-) and the metal wire 102A of the coated wire 102 at the plus potential (+).

In addition, in forming the metal ball 102Aa, the gas from the fluid blast equipment 119 is blasted against the melting and shrinking insulator 102B of the coated wire 102 by the fluid blast nozzles 110C which have been positioned together with the cover member 110A, whereby the insulator 102B is blown away as illustrated in Fig. 20. The insulator 102Ba blown away is drawn by the suction unit 111 through the suction pipe 110.

The gas from the fluid blast nozzles 110C has been cooled down to approximately 0 - -10 [$^{\circ}$ C] by the cooler 119A shown in Fig. 20. Fig. 24 illustrates the relationship between the temperature T_g [$^{\circ}$ C] of the gas (the axis of abscissas) and the magnitude of shrinkable melting L [mm] of the insulator 102B of the coated wire 102 (the axis of ordinates). The flow rate Q of the gas from the fluid blast nozzles 110C is 0.5 - 2.5 [lit./min]. As shown in the figure, as the temperature of the gas from the fluid blast nozzles 110C is lower, the magnitude of shrinkable melting L of the insulator 102B of the coated wire 102 is smaller. That is, since the gas cooled by the cooler 119A can positively cool the metal wire 102A and insulator 102B of the coated wire 102, the bonding tool 107, etc., the insulator 102B in only the area where the electric arcs appear can be melted to lessen the magnitude of shrinkable melting of the insulator 102B.

Subsequently, the cover member 110A is moved in the direction of the arrow A (in the opposite sense to the foregoing) together with both the electric torch 110D and the fluid blast nozzles 110C.

Subsequently, the metal ball 102Aa formed at the front end of the coated wire 102 in the supply direction thereof is drawn toward the pressing face of the bonding tool 107.

Next, under this state, the bonding tool 107 is brought near to the bonding space 103, and as the bonding tool 107 is indicated by phantom lines in Fig. 16, the metal ball 102Aa formed at the front end of the coated wire 102 in the supply direction thereof is joined to the external terminal 120Aa of the semiconductor chip 120A (first bonding). The joining of the metal ball 102Aa is effected by the ultrasonic vibrations and thermocompression (or either of them) of the bonding tool 7.

At the next step, as shown in Fig. 16, the metal wire 102A at the rear end of the coated wire 102 is joined to the lead 102D by the bonding tool 107 (second bonding). The joining of the rear end side of the coated wire 102 is effected by the ultrasonic vibrations and thermocompression (or only the former of them) of the bonding tool 107. As regards the joining of the rear end side of the coated wire 102, the joint part of the coated wire 102 is coated with the insulator 102B beforehand. By the ultrasonic vibrations of the bonding tool 107, however, the insulator 102B in only the joint part is destroyed to denude the metal wire 102A. The insulator (in the case of polyurethane resin) 102B of the coated wire 102 should preferably have a film thickness of about 0.2 - 3 [μ m] though the thickness value somewhat changes depending upon the energy of the ultrasonic vibrations or the force of the thermocompression of the bonding tool 107. In particular, the optimum thickness of the film of the insulator 102B is about 0.2 - 1.0 [μ m]. In a case where the thickness of the insulator 102B of the coated wire 102 is less than 0.2 [μ m], the withstand voltage of the insulator 102B is low. In addition, in a case where the thickness of the insulator 102B of the coated wire 102 is greater than 1.0 [μ m], the insulator 102B becomes

difficult of being destroyed by the ultrasonic vibrations of the bonding tool 107, and in a case where the thickness of the insulator 102B is greater than 3.0 [μm], the insulator 102B is not destroyed. Therefore, the joining between the metal wire 102A of the coated wire 102 and the lead 102D becomes defective.

Subsequently, the bonding tool 107 is brought away (on this occasion, the coated wire 102 is cut), whereby the bonding process is completed as shown in Fig. 16.

In this manner, in the bonding technology wherein the metal ball 102Aa is formed at the front end of the coated wire 102, the fluid blast nozzles 110C (part of the fluid blast equipment 119) for blasting the gas against the front end part of the coated wire 102 are disposed near the front end of the coated wire 102, whereby the melting and shrinking insulator 102B of the coated wire 102 can be blown away, so that the coated wire 102 can be prevented from being formed with the insulator globes. As a result, the catch of the coated wire 102 in the bonding tool 107 attributed to the insulator globes is prevented, and the coated wire 102 can be drawn to the pressing face of the bonding tool 107, so that the ball bonding can be performed, and a bonding defect is avoidable.

Besides, in the bonding technology wherein the metal ball 102Aa is formed at the front end of the coated wire 102, the fluid blast nozzles 110C (the fluid blast equipment 119) stated above is disposed, and the suction pipe 110e (the suction unit 111) which draws the insulator 102B of the coated wire 102 blown away by the blast of the gas from the fluid blast nozzles 110C is disposed near the front end of the coated wire 102, whereby the melting and shrinking insulator 102B of the coated wire 102 can be blown away to prevent the formation of the insulator globes in the coated wire 102 and to avoid the bonding defect as described above, and moreover, the insulator 102Ba blown away is prevented from scattering to the bonding space 103, so that a bonding defect attributed to the scattered insulator 102Ba is avoidable. The bonding defect attributed to the scattered insulator 102Ba signifies, for example, a case where the insulator 102Ba scatters to a position the external terminal 120Aa of the semiconductor chip 120A or the lead 120D and the metal wire 102A of the coated wire 102, so the continuity between the two becomes inferior.

Further, in the bonding technology wherein the metal ball 102Aa is formed at the front end of the coated wire 102, the fluid blast nozzles 110C (the fluid blast equipment 119) stated above are disposed, and the cooler 119A for cooling the gas of the fluid blast nozzles 110C is disposed, whereby the shrinkable melting of the insulator 102B of the coated wire 102 is remarkably reduced, and even when the insulator 102B has melted and shrunk, it can be blown away, so that the formation of the insulator globes in the coated wire 102 is prevented, and the bonding defect is avoidable as described before.

Further, in the bonding technology which uses the coated wire 102, the metal ball 102Aa is formed on the front end side of the coated wire 102 in the supply direction thereof, and it is joined to the external terminal 120Aa of the semiconductor chip 120A, while the rear end side of the coated wire 102 in the supply direction thereof is brought into contact with the lead 120D, the insulator 102B at the contact part is destroyed, and the metal wire 102A on the other end side of the coated wire 102 is joined to the lead 120D, whereby the insulator 102B can be removed without using an insulator removal torch which removes the insulator 102B on the rear end side of the coated wire 102, so that the insulator removal torch, and moving mechanisms and controllers therefor can be dispensed with. As a result, the structure of the bonding apparatus can be simplified.

Embodiment 6:

Embodiment 6 is another embodiment of the present invention in which the construction of the fluid blast equipment of the ball-bonding apparatus is altered.

The essential portions of the ball-bonding apparatus which is Embodiment 6 of the present invention are shown in Fig. 25 (a partial sectional view) and Fig. 26 (a plan view seen in the direction of arrow XIV in Fig. 25).

As illustrated in Figs. 25 and 26, the fluid blast nozzle 110C of the fluid blast equipment 119 (not shown) in the present embodiment 6 is so configured that a U-shaped fluid conveyance pipe is provided with pores for blasting the gas. This fluid blast nozzle 110C in the shape of letter U is fastened to the bonding apparatus proper, for example, the X-Y table 117.

The suction pipe 110E of the suction unit 111 (not shown) is oriented in the direction in which the gas from the U-shaped fluid blast nozzle 110C is blasted. Likewise to the fluid blast nozzle 110C, the suction pipe 110E is fastened to the bonding apparatus proper, for example, the X-Y table 117.

The electric torch 110D is constructed so as to move and turn in the direction of arrow A substantially in the same manner as in Embodiment 5. That is, the electric torch 110D is adapted to move to a position where the gas is blasted from the fluid blast nozzle 110C, when the metal ball 102Aa is formed at the front end of the coated wire 102 in the supply direction thereof, and to thereafter come away from the position when the bonding ball 102Aa is bonded. The movement of the electric torch 110D is effected by a moving mechanism

110L which is fastened to the bonding apparatus proper, for example, the X-Y table 117.

The fluid blast nozzle 110C, the suction pipe 110E and the electric torch 110D are directly fastened to the bonding apparatus proper because the cover member 110A disposed in Embodiment 5 is not included.

With the ball-bonding apparatus thus constructed, when the metal ball 102Aa is formed at the front end of the coated wire 102 in the supply direction thereof, an operator can observe the front end part. It is therefore possible to optimize the state of generation of the electric arcs, the state of blast of the gas from the fluid blast nozzle 110C, the state of suction of the insulator 102B scattered by the gas, and so on.

The present invention is not restricted to the resin-encapsulated semiconductor device, but it is applicable to the semiconductor technology of a ceramic-encapsulated semiconductor device.

Claims

1. A method for bonding a metal wire to a semiconductor device; the device having a semiconductor chip (12A,120A) with at least one bonding site (12Aa,120Aa) on a major surface thereof and at least one lead (12D,120D); the method using a bonder having a bonding stage (3,113), a capillary (7,107), a spool (12,101) coiled with a wire (2,102) coated by an insulating film of an organic resin (2B,102B) and a discharge electrode (10, 110D); the method comprising the steps of:
 - (a) placing the chip (12A,120A) on the bonding stage (3,113);
 - (b) causing one end of the wire (2,102) to project through the capillary (7,107);
 - (c) generating an arc discharge between the one end of the wire (2,102) projecting through the capillary (7,107) and the electrode (10,110D) by applying a first electric potential to the other end of the wire (2,102) coiled on the spool (12,101) and a second electric potential to the electrode (10,110D) to form a ball on the one end of the wire (2,102); and then
 - (d) bonding the wire to the bonding site by pressing the ball against the bonding site using the capillary (7);

characterised in that:

the step (c) is performed while vapor of the organic resin (2B,102B), which vapor is produced by the heat of the arc discharge, is evacuated through an evacuating nozzle (16,110E) adjacent to the one end of the wire (2,102) to prevent the vapor from condensing on or in the capillary (7,107).
2. A method for bonding a metal wire to a semiconductor device; the device having a semiconductor chip (12A,120A) with at least one bonding site (12Aa,120Aa) on a major surface thereof and at least one lead (12D,120D); the method using a bonder having a bonding stage (3,113), a capillary (7,107), a spool (12,101) coiled with a wire (2,102) coated by an insulating film of an organic resin (2B,102B) and a discharge electrode (10,110D); the method comprising the steps of:
 - (a) placing the chip (12A,120A) on the bonding stage (3,113);
 - (b) causing one end of the wire (2,102) to project through the capillary (7,107);
 - (c) generating an arc discharge between the one end of the wire (2,102) projecting through the capillary and the electrode (10,110D) by applying a first electric potential to the other end of the wire (2,102) coiled on the spool and a second electric potential to the electrode (10,110D) to form a ball on the one end of the wire (12,101); and then
 - (d) bonding the wire to the bonding site by pressing the ball against the bonding site using the capillary (7,107);
 - (e) removing the insulating film (2B,112B) of the wire by vaporizing the insulating film (2B,112B) with heat over a predetermined length at a predetermined point of the wire (2,102) between the one and the other ends of the wire (2,102) to be bonded to the lead while the one end of the wire (2,102) protrudes out of the capillary; and then
 - (f) wedge-bonding the predetermined point of the wire (2,102) to the lead by pressing the predetermined point of the wire (2,102) against the lead with the capillary;

characterised in that:

the step (e) is performed while vapor of the organic resin (2B,102B), which vapor is produced by the heat, is evacuated through an evacuating nozzle (16) adjacent to the predetermined point of the wire (2,102) to prevent the vapor from condensing on or in the bonder.
3. A method according to claim 1 or claim 2, wherein the first electric potential is positive relative to the second electric potential.



110L which is fastened to the bonding apparatus proper, for example, the X-Y table 117.

The fluid blast nozzle 110C, the suction pipe 110E and the electric torch 110D are directly fastened to the bonding apparatus proper because the cover member 110A disposed in Embodiment 5 is not included.

5 With the ball-bonding apparatus thus constructed, when the metal ball 102Aa is formed at the front end of the coated wire 102 in the supply direction thereof, an operator can observe the front end part. It is therefore possible to optimize the state of generation of the electric arcs, the state of blast of the gas from the fluid blast nozzle 110C, the state of suction of the insulator 102B scattered by the gas, and so on.

The present invention is not restricted to the resin-encapsulated semiconductor device, but it is applicable to the semiconductor technology of a ceramic-encapsulated semiconductor device.

10

Claims

- 15 1. A method for bonding a metal wire to a semiconductor device; the device having a semiconductor chip (12A,120A) with at least one bonding site (12Aa,120Aa) on a major surface thereof and at least one lead (12D,120D); the method using a bonder having a bonding stage (3,113), a capillary (7,107), a spool (12,101) coiled with a wire (2,102) coated by an insulating film of an organic resin (2B,102B) and a discharge electrode (10, 110D); the method comprising the steps of:
 - 20 (a) placing the chip (12A,120A) on the bonding stage (3,113);
 - (b) causing one end of the wire (2,102) to project through the capillary (7,107);
 - (c) generating an arc discharge between the one end of the wire (2,102) projecting through the capillary (7,107) and the electrode (10,110D) by applying a first electric potential to the other end of the wire (2,102) coiled on the spool (12,101) and a second electric potential to the electrode (10,110D) to form a ball on the one end of the wire (2,102); and then
 - 25 (d) bonding the wire to the bonding site by pressing the ball against the bonding site using the capillary (7);

characterised in that:

the step (c) is performed while vapor of the organic resin (2B,102B), which vapor is produced by the heat of the arc discharge, is evacuated through an evacuating nozzle (16,110E) adjacent to the one end of the wire (2,102) to prevent the vapor from condensing on or in the capillary (7,107).
- 30 2. A method for bonding a metal wire to a semiconductor device; the device having a semiconductor chip (12A,120A) with at least one bonding site (12Aa,120Aa) on a major surface thereof and at least one lead (12D,120D); the method using a bonder having a bonding stage (3,113), a capillary (7,107), a spool (12,101) coiled with a wire (2,102) coated by an insulating film of an organic resin (2B,102B) and a discharge electrode (10,110D); the method comprising the steps of:
 - 35 (a) placing the chip (12A,120A) on the bonding stage (3,113);
 - (b) causing one end of the wire (2,102) to project through the capillary (7,107);
 - (c) generating an arc discharge between the one end of the wire (2,102) projecting through the capillary and the electrode (10,110D) by applying a first electric potential to the other end of the wire (2,102) coiled on the spool and a second electric potential to the electrode (10,110D) to form a ball on the one end of the wire (12,101); and then
 - 40 (d) bonding the wire to the bonding site by pressing the ball against the bonding site using the capillary (7,107);
 - (e) removing the insulating film (2B,112B) of the wire by vaporizing the insulating film (2B,112B) with heat over a predetermined length at a predetermined point of the wire (2,102) between the one and the other ends of the wire (2,102) to be bonded to the lead while the one end of the wire (2,102) protrudes out of the capillary; and then
 - 45 (f) wedge-bonding the predetermined point of the wire (2,102) to the lead by pressing the predetermined point of the wire (2,102) against the lead with the capillary;
 - 50 (g) characterised in that:
 - the step (e) is performed while vapor of the organic resin (2B,102B), which vapor is produced by the heat, is evacuated through an evacuating nozzle (16) adjacent to the predetermined point of the wire (2,102) to prevent the vapor from condensing on or in the bonder.
- 55 3. A method according to claim 1 or claim 2, wherein the first electric potential is positive relative to the second electric potential.



4. A method according to any one of the preceding claims, wherein steps (c) and (d) are performed while the other end of the wire (2,102) is connected to a common ground electric potential of the bonder so as to prevent an undesirable discharge between the wire (2,102) and the bonder.
5. A method according to claim 4, wherein the common ground is electrically common with the ground of an arc generator for generating the first and second potential.
6. A method according to any one of the preceding claims wherein the spool (12,101) is of a metal.
7. A method according to any one of the preceding claims, wherein the spool (12,101) is of aluminium.
8. A method according to any one of the preceding claims wherein the wire (2,102) is of gold.
9. A method according to any one of the preceding claims, wherein the thin insulating film is of a polyurethane resin.
10. An apparatus for bonding a metal wire coated by an organic insulating film to an electronic device, the device having a semiconductor chip (12A,120A) with at least one bonding site (12Aa,120Aa) on a major surface thereof and at least one lead (12D,120D); said apparatus comprising:
- (a) a wire bonding stage (3,113) for receiving the chip (12A,120A);
 - (b) a bonding wire (2,102) coated by an organic insulating film (2B,102B) coiled on a spool (12,101), and a bonding capillary (7,107) arranged so as to permit one end of the wire (2,102) to project from a lower tip thereof through its bore;
 - (c) a discharge electrode (10,110D) above the stage;
 - (d) an arc voltage generator for generating an arc discharge through a gap between the one end of the wire (2,102) projecting through the capillary (7,107) and the electrode (10,110D) by applying a first electric potential to the wire (2,102) via the other end of the wire (2,102) coiled on the spool (12,101) and a second electric potential to the electrode thereby to form a ball at the one end of the wire (2,102); and
 - (e) a control means for bonding the wire (2,102) to the bonding site on the chip (12A,120A) by pressing the ball against the site with the lower tip of the capillary (7,107);
- characterised in that the apparatus further comprises an evacuating nozzle (16,110E) adjacent to the lower tip of the capillary (7,107) for evacuating vapor of the organic film (2B,102B) produced by the heat of the arc discharge.
11. An apparatus according to claim 10, further comprising:
- (g) a torch (15) for generating heat to remove the insulating film (2B,102B) over a predetermined length at a predetermined point of the wire (2,102) between the one and the other ends of the wire (2,102) to be wedge-bonded by the capillary;
 - (h) a further evacuating nozzle (16) for evacuating vapor of the insulating film (2B,102B) produced by the heat during the removal of the insulating film (2B,102B) at the predetermined point of the wire (2,102) to prevent the vapor from condensing on or in the bonder.
12. An apparatus for bonding a metal wire coated by an organic insulating film to an electronic device, the device having a semiconductor chip (12A,120A) with at least one bonding site (12Aa,120Aa) on a major surface thereof and at least one lead (12D,120D); said apparatus comprising:
- (a) a wire bonding stage (3,103) for receiving the chip (12A,120A);
 - (b) a bonding wire (2,102) coated by an organic insulating film (2B,102B) coiled on a spool (12,101), and a bonding capillary (7,107) arranged so as to permit one end of the wire (2,102) to project from a lower tip thereof through its bore;
 - (c) a discharge electrode (10,110D) above the stage;
 - (d) an arc voltage generator for generating an arc discharge through a gap between the one end of the wire (2,102) projecting through the capillary (7,107) and the electrode by applying a first electric potential to the wire (2,102) via the other end of the wire (2,102) coiled on the spool (12,101) and a second electric potential to the electrode thereby to form a ball at the one end of the wire (2,102); and
 - (e) a control means for bonding the wire (2,102) to the bonding site on the chip (12A,120A) by pressing the ball against the site with the lower tip of the capillary (7,107);
- characterised in that the apparatus further comprises:
- (f) a torch (15) for generating heat to remove the insulating film (2B,102B) over a predetermined length



at a predetermined point of the wire (2,102) between the one and the other ends of the wire (2,102) to be wedge-bonded by the capillary, while the one end of the wire (2,102) protrudes out of the lower tip of the capillary (7,107);

(g) an evacuating nozzle (16) for evacuating vapor of the insulating film (2B,102B) produced by the heat during the removal of the insulating film (2B,102B) at the predetermined point of the wire to prevent the vapor from condensing on or in the bonder; and

(h) a control means for wedge-bonding the predetermined point of the wire (2,102) to the lead by pressing the predetermined point of the wire (2,102) against the lead with the capillary (7,107).

Patentansprüche

1. Verfahren zum Anbonden eines Metalldrahts an ein Halbleiter-Bauelement, das einen Halbleiterchip (12A, 120A) mit mindestens einem Bondort (12Aa, 120Aa) auf einer seiner Hauptflächen und mindestens eine Zuleitung (12D, 120D) aufweist; welches Verfahren eine Bondeinrichtung mit einem Bondtisch (3, 113), eine Kapillare (7, 107), eine Spule (12, 101) mit einem aufgewickelten Draht (2, 102), der mit einem Isolierfilm aus organischem Harz (2B, 102B) beschichtet ist, und eine Entladeelektrode (10, 110D) verwendet und das folgende Schritte aufweist:

(a) Anordnen des Chips (12A, 120A) auf dem Bondtisch (3, 113);

(b) Bewirken, daß ein Ende des Drahts (2, 102) über die Kapillare (7, 107) übersteht;

(c) Erzeugen einer Probenentladung zwischen dem einen Ende des Drahts (2, 102), das über die Kapillare (7, 107) übersteht, und der Elektrode (10, 110D) durch Anlegen eines ersten elektrischen Potentials an das andere Ende des auf die Spule (12, 101) aufgewickelten Drahts (2, 102) und eines zweiten elektrischen Potentials an die Elektrode (10, 110D), um eine Kugel am einen Ende des Drahts (2, 102) auszubilden; und dann

(d) Anbonden des Drahts an den Bondort durch Andrücken der Kugel gegen den Bondort unter Verwendung der Kapillare (7);

dadurch gekennzeichnet, daß:

- der Schritt (c) ausgeführt wird, während Dampf des organischen Harzes (2B, 102B), der durch die Wärme der Bogenentladung erzeugt wird, durch eine Abpumpdüse (16, 110E) abgepumpt wird, die neben dem einen Ende des Drahts (2, 102) liegt, um zu verhindern, daß der Dampf an oder in der Kapillare (7, 107) kondensiert.

2. Verfahren zum Anbonden eines Metalldrahts an ein Halbleiter-Bauelement, das einen Halbleiterchip (12A, 120A) mit mindestens einem Bondort (12Aa, 120Aa) auf einer seiner Hauptflächen und mindestens eine Zuleitung (12D, 120D) aufweist; welches Verfahren eine Bondeinrichtung mit einem Bondtisch (3, 113), eine Kapillare (7, 107), eine Spule (12, 101) mit einem aufgewickelten Draht (2, 102), der mit einem Isolierfilm aus organischem Harz (2B, 102B) beschichtet ist, und eine Entladeelektrode (10, 110D) verwendet und das folgende Schritte aufweist:

(a) Anordnen des Chips (12A, 120A) auf dem Bondtisch (3, 113);

(b) Bewirken, daß ein Ende des Drahts (2, 102) durch die Kapillare (7, 107) hindurch vorsteht;

(c) Erzeugen einer Bogenentladung zwischen dem einen Ende des Drahts (2, 102), das über die Kapillare (7, 107) übersteht, und der Elektrode (10, 110D) durch Anlegen eines ersten elektrischen Potentials an das andere Ende des auf die Spule (12, 101) aufgewickelten Drahts (2, 102) und eines zweiten elektrischen Potentials an die Elektrode (10, 110D), um eine Kugel am einen Ende des Drahts (2, 102) auszubilden; und dann

(d) Anbonden des Drahts an den Bondort durch Andrücken der Kugel gegen den Bondort unter Verwendung der Kapillare (7, 107);

(e) Entfernen des Isolierfilms (2B, 112B) des Drahts durch Verdampfen des Isolierfilms (2B, 112B) mit Wärme über eine vorgegebene Länge an einem vorgegebenen Punkt des Drahts (2, 102) zwischen dem einen und dem anderen Ende des Drahts (2, 102), wie an der Zuleitung anzubonden, während das andere Ende des Drahts (2, 102) aus der Kapillare heraussteht; und dann

(f) Verbinden des vorgegebenen Punkts des Drahts (2, 102) durch Keilbonden mit der Zuleitung durch Andrücken des vorgegebenen Punkts des Drahts (2, 102) mit der Kapillare gegen die Zuleitung;

dadurch gekennzeichnet, daß:

- der Schritt (e) ausgeführt wird, während Dampf des organischen Harzes (2B, 102B), der durch die Wärme der Bogenentladung erzeugt wird, durch eine Abpumpdüse (16, 110E) abgepumpt wird, die neben dem einen Ende des Drahts (2, 102) liegt, um zu verhindern, daß der Dampf an oder in der Bond-



einrichtung kondensiert.

3. Verfahren nach Anspruch 1 oder Anspruch 2, bei dem das erste elektrische Potential positiv in bezug auf das zweite elektrische Potential ist.
- 5 4. Verfahren nach einem der vorstehenden Ansprüche, bei dem die Schritte (c) und (d) ausgeführt werden, während das andere Ende des Drahts (2, 102) mit gemeinsamem, elektrischem Massepotential der Bond-einrichtung verbunden ist, um eine unerwünschte Entladung zwischen dem Draht (2, 102) und der Bond-einrichtung zu verhindern.
- 10 5. Verfahren nach Anspruch 4, bei dem die gemeinsame Masse elektrisch der Masse eines Bogengenerators zum Erzeugen des ersten und zweiten Potentials gemeinsam ist.
6. Verfahren nach einem der vorstehenden Ansprüche, bei dem die Spule (12, 101) aus Metall besteht.
- 15 7. Verfahren nach einem der vorstehenden Ansprüche, bei dem die Spule (12, 101) aus Aluminium besteht.
8. Verfahren nach einem der vorstehenden Ansprüche, bei dem der Draht (2, 102) aus Gold besteht.
9. Verfahren nach einem der vorstehenden Ansprüche, bei dem der dünne Isolierfilm aus Polyurethanharz besteht.
- 20 10. Vorrichtung zum Anbonden eines mit einem organischen Isolierfilm beschichteten Metalldrahts an ein elektronisches Bauelement, das einen Halbleiterchip (12A, 120A) mit mindestens einem Bondort (12Aa, 120Aa) auf einer seiner Hauptflächen und mindestens eine Zuleitung (12D, 120D) aufweist; welche Vorrichtung folgendes aufweist:
 - 25 (a) einen Drahtbondtisch (3, 113) zum Aufnehmen des Chips (12A, 120A);
 - (b) einen Bonddraht (2, 102), der mit einem organischen Isolierfilm (2B, 102B) beschichtet und auf einer Spule (12, 101) aufgewickelt ist, und mit einer Bondkapillare (7, 107), die so angeordnet ist, daß ein Ende des Drahts (2, 102) aus ihrer unteren Spitze durch ihre Bohrung hindurch vorstehen kann;
 - 30 (c) eine Entladeelektrode (10, 110D) über dem Tisch;
 - (d) einen Bogen-Spannungsgenerator zum Erzeugen einer Bogenentladung über einen Spalt zwischen dem einen Ende des durch die Kapillare (7, 107) hindurch vorstehenden Drahts (2, 102) und der Elektrode (10, 110D) durch Anlegen eines ersten elektrischen Potentials an den Draht (2, 102) über das andere Ende des auf die Spule (12, 101) aufgewickelten Drahts (2, 102), und eines zweiten elektrischen Potentials an die Elektrode, um dadurch am einen Ende des Drahts (2, 102) eine Kugel ausbilden; und
 - 35 (e) eine Steuereinrichtung zum Anbonden des Drahts (2, 102) am Bondort an den Chip (12A, 120A) durch Andrücken der Kugel mit der unteren Spitze der Kapillare (7, 107) gegen den Ort; dadurch gekennzeichnet, daß die Vorrichtung ferner eine Abpumpdüse (16, 110E) neben der unteren Spitze der Kapillare (7, 107) zum Abpumpen von Dampf des organischen Films (2B, 102B) aufweist, wie er durch die Hitze der Bogenentladung erzeugt wird.
 - 40
11. Vorrichtung nach Anspruch 10, ferner mit:
 - (g) einem Brenner (15) zum Erzeugen von Wärme zum Entfernen des Isolierfilms (2B, 102B) über eine vorgegebene Länge an einem vorgegebenen Punkt des Drahts (2, 102) zwischen dem einen und dem anderen Ende des Drahts (2, 102), der durch die Kapillare einem Keilbondvorgang zu unterziehen ist;
 - 45 (h) einer weiteren Abpumpdüse (16) zum Abpumpen von Dampf des Isolierfilms (2B, 102B), wie er durch die Wärme während des Entferns des Isolierfilms (2B, 102B) am vorgegebenen Punkt des Drahts (2, 102) erzeugt wird, um zu verhindern, daß Dampf an oder in der Bondeinrichtung kondensiert.
- 50 12. Vorrichtung zum Anbonden eines mit einem organischen Isolierfilm beschichteten Metalldrahts an ein elektronisches Bauelement, das einen Halbleiterchip (12A, 120A) mit mindestens einem Bondort (12Aa, 120Aa) auf einer seiner Hauptflächen und mindestens eine Zuleitung (12D, 120D) aufweist; welche Vorrichtung folgendes aufweist:
 - (a) einen Drahtbondtisch (3, 113) zum Aufnehmen des Chips (12A, 120A);
 - 55 (b) einen Bonddraht (2, 102), der mit einem organischen Isolierfilm (2B, 102B) beschichtet und auf einer Spule (12, 101) aufgewickelt ist, und mit einer Bondkapillare (7, 107), die so angeordnet ist, daß ein Ende des Drahts (2, 102) aus ihrer unteren Spitze durch ihre Bohrung hindurch vorstehen kann;
 - (c) eine Entladeelektrode (10, 110D) über dem Tisch;



(d) einen Bogen-Spannungsgenerator zum Erzeugen einer Bogenentladung über einen Spalt zwischen dem einen Ende des durch die Kapillare (7, 107) hindurch vorstehenden Drahts (2, 102) und der Elektrode (10, 110D) durch Anlegen eines ersten elektrischen Potentials an den Draht (2, 102) über das andere Ende des auf die Spule (12, 101) aufgewickelten Drahts (2, 102), und eines zweiten elektrischen Potentials an die Elektrode, um dadurch am einen Ende des Drahts (2, 102) eine Kugel ausbilden; und (e) eine Steuereinrichtung zum Anbonds des Drahts (2, 102) am Bondort an den Chip (12A, 120A) durch Andrücken der Kugel mit der untersten Spitze der Kapillare (7, 107) gegen den Ort; dadurch gekennzeichnet, daß die Vorrichtung ferner folgendes aufweist:

(f) einen Brenner (15) zum Erzeugen von Wärme zum Entfernen des Isolierfilms (2B, 102B) über eine vorgegebene Länge an einem vorgegebenen Punkt des Drahts (2, 102) zwischen dem einen und dem anderen Ende des Drahts (2, 102), der durch die Kapillare einem Keilbondvorgang zu unterziehen ist, während das eine Ende des Drahts (2, 102) aus der unteren Spitze der Kapillare (7, 107) hervorsteht; (g) eine Abpumpdüse (16) zum Abpumpen von Dampf des Isolierfilms (2B, 102B), wie er durch die Wärme während des Entferns des Isolierfilms (2B, 102B) am vorgegebenen Punkt des Drahts (2, 102) erzeugt wird, um zu verhindern, daß Dampf an oder in der Bondeinrichtung kondensiert; und (h) eine Steuereinrichtung zum Ausführen eines Keilbondvorgangs zwischen dem vorgegebenen Punkt des Drahts (2, 102) und der Zuleitung durch Andrücken des vorgegebenen Punkts des Drahts (2, 102) an die Zuleitung mit Hilfe der Kapillare (7, 107).

Revendications

1. Procédé pour réunir un fil métallique à un dispositif à semiconducteurs; le dispositif possédant une microplaquette à semiconducteurs (12A, 120A) comportant au moins un site de liaison (12Aa, 120Aa) situé sur une surface principale de la microplaquette et au moins un conducteur (12D, 120D); le procédé utilisant un dispositif de liaison possédant une table de liaison (3, 113), un capillaire (7, 107), une bobine (12, 101) sur laquelle est bobiné un fil (2, 102) recouvert d'une pellicule isolante formée d'une résine organique (2B, 102B), et une électrode de décharge (10, 110D); le procédé comprenant les étapes consistant à :

- (a) placer la microplaquette (12A, 120A) sur la table de liaison (3, 113);
- (b) amener une première extrémité du fil (2, 102) à traverser le capillaire (7, 107);
- (c) produire une décharge par arc entre la première extrémité du fil (2, 102) pénétrant dans le capillaire (7, 107), et l'électrode (10, 110D) par application d'un premier potentiel électrique à l'autre extrémité du fil (2, 102) enroulé sur la bobine (12, 101), et d'un second potentiel électrique à l'électrode (10, 110D) pour former une boule sur la première extrémité du fil (2, 102); puis
- (d) réunir le fil au site de liaison par compression de la boule contre le site de liaison moyennant l'utilisation du capillaire (7);

caractérisé en ce que :

l'étape (c) est exécutée alors que la vapeur de la résine organique (2B, 102B), qui est produite par la chaleur de la décharge par arc, est évacuée par l'intermédiaire d'une buse d'évacuation (16, 110E) adjacente à une extrémité du fil (2, 102) de manière à empêcher une condensation de la vapeur sur ou dans le capillaire (7, 107).

2. Procédé pour réunir un fil métallique à un dispositif à semiconducteurs; le dispositif possédant une microplaquette à semiconducteurs (12A, 120A) comportant au moins un site de liaison (12Aa, 120Aa) situé sur une surface principale de la microplaquette et au moins un conducteur (12D, 120D); le procédé utilisant un dispositif de liaison possédant une table de liaison (3, 113), un capillaire (7, 107), une bobine (12, 101) sur laquelle est bobiné un fil (2, 102) recouvert d'une pellicule isolante formée d'une résine organique (2B, 102B), et une électrode de décharge (10, 110D); le procédé comprenant les étapes consistant à :

- (a) placer la microplaquette (12A, 120A) sur la table de liaison (3, 113);
- (b) amener une première extrémité du fil (2, 102) à traverser le capillaire (7, 107);
- (c) produire une décharge par arc entre la première extrémité du fil (2, 102) pénétrant dans le capillaire (7, 107), et l'électrode (10, 110D) par application d'un premier potentiel électrique à l'autre extrémité du fil (2, 102) enroulé sur la bobine (12, 101), et d'un second potentiel électrique à l'électrode (10, 110D) pour former une boule sur la première extrémité du fil (2, 102); puis
- (d) réunir le fil au site de liaison par compression de la boule contre le site de liaison moyennant l'utilisation du capillaire (7);



- (e) éliminer la pellicule isolante (2B,112B) du fil en déposant par évaporation la pellicule isolante (2B,112B), moyennant l'application d'une chaleur, sur une longueur prédéterminée en un point prédéterminé du fil (2,102) entre la première extrémité et l'autre extrémité du fil (2,102) devant être réuni au conducteur, alors que la première extrémité du fil (2,102) fait saillie hors du capillaire; et
- (f) réunir par pincement le point prédéterminé du fil (2, 102) au conducteur en comprimant le point prédéterminé du fil (2,102) contre le conducteur avec le capillaire;
- caractérisé en ce que :
- l'étape (e) est exécutée alors que la vapeur de la résine organique (2B,102B), qui est produite par la chaleur de la décharge par arc, est évacuée par l'intermédiaire d'une buse d'évacuation (16) adjacente au point prédéterminé du fil (2,102) de manière à empêcher une condensation de la vapeur sur ou dans le dispositif de liaison.
3. Procédé selon la revendication 1 ou 2, dans lequel le premier potentiel électrique est positif par rapport au second potentiel électrique.
 4. Procédé selon l'une quelconque des revendications précédentes, dans lequel les étapes (c) et (d) sont exécutées alors que l'autre extrémité du fil (2,102) est raccordée à un potentiel électrique de masse commun du dispositif de liaison de manière à empêcher une décharge indésirable entre le fil (2,102) et le dispositif de liaison.
 5. Procédé selon la revendication 4, dans lequel la masse commune est raccordée électriquement à la masse d'un générateur d'arc pour la production des premier et second potentiels.
 6. Procédé selon l'une quelconque des revendications précédentes, dans lequel la bobine (12,101) est formée d'un métal.
 7. Procédé selon l'une quelconque des revendications précédentes, dans lequel la bobine (12,101) est réalisée en aluminium.
 8. Procédé selon l'une quelconque des revendications précédentes, dans lequel le fil (2,102) est en or.
 9. Procédé selon l'une quelconque des revendications précédentes, dans lequel la pellicule mince isolante est formée d'une résine polyuréthane.
 10. Appareil pour réunir un fil métallique pour recouvrir par une pellicule organique isolante un dispositif électronique, le dispositif comprenant une microplaquette à semiconducteurs (12A,120A) comportant au moins un site de liaison (12Aa,120Aa) sur une surface principale de la microplaquette et au moins un conducteur (12D,120D); ledit appareil comprenant :
 - (a) une table de liaison de fil (3,113) servant à recevoir la microplaquette (12A,120A);
 - (b) un fil de liaison (2,102) recouvert d'une pellicule organique isolante (2B,102B) enroulée sur une bobine (12,101) et un capillaire de liaison (7,107) disposé de telle sorte qu'une première extrémité du fil (2,102) fait saillie, à partir de la pointe inférieure du capillaire, à travers le perçage de ce dernier;
 - (c) une électrode de décharge (10,110D) disposée au-dessus de la table;
 - (d) un générateur de tension à arc servant à produire une décharge à arc dans un espace situé entre la première extrémité du fil (2,102) qui traverse le capillaire (7,107), et l'électrode (10,110D) par application d'un premier potentiel électrique au fil (2,102) par l'intermédiaire de l'autre extrémité du fil (2,102) enroulé sur la bobine (12,101), et d'un second potentiel électrique à l'électrode de manière à former une boule au niveau de la première extrémité du fil (2,102); et
 - (e) des moyens de commande pour réunir le fil (2,102) au site de liaison situé sur la microplaquette (12A,120A) par compression de la boule contre le site, à l'aide de la pointe inférieure du capillaire (7,107);
 caractérisé en ce que l'appareil comporte en outre une buse d'évacuation (16,110E) située au voisinage de la pointe inférieure du capillaire (7,107) pour évacuer la vapeur de la pellicule organique (2B,102B) produite par la chaleur de la décharge à arc.
 11. Appareil selon la revendication 10, comprenant en outre :
 - (g) un chalumeau (15) servant à produire la chaleur pour éliminer la pellicule isolante (2B,102B) sur une longueur prédéterminée en un point prédéterminé du fil (2,102) entre la première extrémité et l'autre extrémité du fil (2,102), de manière à le fixer par une liaison par pincement au moyen du capillaire;



(h) une autre buse d'évacuation (16) servant à évacuer une vapeur de la pellicule isolante (2B,102B) produite par la chaleur au cours de l'enlèvement de la pellicule isolante (2B,102B) au niveau du point prédéterminé du fil (2,102) pour empêcher une condensation de la vapeur sur ou dans le dispositif de liaison.

5
12. Appareil pour réunir un fil métallique recouvert d'une pellicule organique isolante à un dispositif électronique, le dispositif possédant une microplaquette à semiconducteurs (12A,120A) possédant au moins un site de liaison (12Aa,120Aa) sur une surface principale de la microplaquette, et au moins un conducteur (12D,120D); ledit appareil comprenant :

10 (a) une table de liaison de fil (3,103) servant à recevoir la microplaquette (12A,120A);

(b) un fil de liaison (2,102) recouvert d'une pellicule organique isolante (2B,102B) enroulée sur une bobine (12,101) et un capillaire de liaison (7,107) disposé de manière à permettre à une première extrémité du fil (2,102) de faire saillie, à partir de la pointe inférieure du capillaire, à travers le perçage de ce dernier;

15 (c) une électrode de décharge (10,110D) disposée au-dessus de la table;

(d) un générateur de tension à arc servant à produire une décharge à arc dans un intervalle situé entre la première extrémité du fil (2,102) qui traverse le capillaire (7,107), et l'électrode par application d'un premier potentiel électrique au fil (2,102) par l'intermédiaire de l'autre extrémité du fil (2,102) enroulé sur la bobine (12,101), et d'un second potentiel électrique à l'électrode de manière à former une boule au niveau de la première extrémité du fil (2,102); et

20 (e) des moyens de commande pour réunir le fil (2,102) au site de liaison situé sur la microplaquette (12A,120A) par compression de la boule contre le site, à l'aide de la pointe inférieure du capillaire (7,107);

caractérisé en ce que l'appareil comporte en outre

25 (f) un chalumeau (15) servant à produire la chaleur pour éliminer la pellicule isolante (2B,102B) sur une longueur prédéterminée en un point prédéterminé du fil (2,102) entre la première extrémité et l'autre extrémité du fil (2,102), de manière à le fixer par une liaison par pincement au moyen du capillaire, alors que la première extrémité du fil (2,102) fait saillie hors de la pointe inférieure du capillaire (7,107);

30 (g) une buse d'évacuation (16) servant à évacuer une vapeur de la pellicule isolante (2B,102B) produite par la chaleur au cours de l'enlèvement de la pellicule isolante (2B,102B) au niveau du point prédéterminé du fil pour empêcher une condensation de la vapeur sur ou dans le dispositif de liaison; et

(h) des moyens de commande pour réunir selon une liaison par pincement le point prédéterminé du fil (2,102) au conducteur par application sous pression du point prédéterminé du fil (2,102) contre le conducteur, au moyen du capillaire (7,107).